

# **ECE 205 “Electrical and Electronics Circuits”**

**Spring 2024 – LECTURE 27**

MWF – 12:00pm

**Prof. Umberto Ravaioli**

2062 ECE Building

# Lecture 27 – Summary

## Learning Objectives

1. Graphical use of  $I$ - $V$  curves
2. Transistor as diode
3. Single Battery Bias of BJT
4. Discussion on BJT amplifier circuits

# Quiz 3 next week - Reminder

- **Four problems:**
  - Two on circuit analysis using phasors
  - Two on diode circuits

**HINT:** read problems very carefully. Do not answer a “different” question.

**No Class on 4/1/2024**

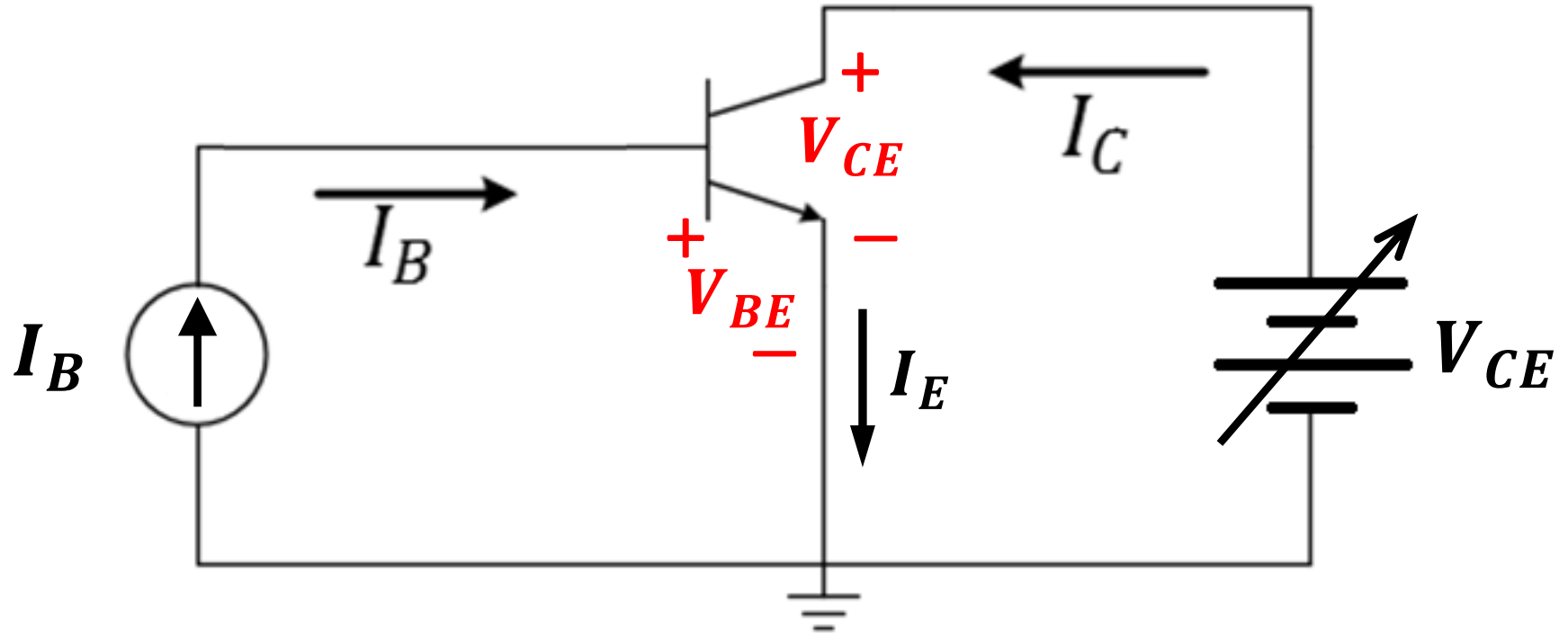
# Practice material on BJT (not on Quiz 3)

- **BJT REVIEW PROBLEMS video Part 1**
  - Basic practice problems on  $n-p-n$  BJTs, including a circuit with resistor on the emitter
- **BJT REVIEW PROBLEMS video Part 2**
  - Discussion on the BJT Darlington pair explaining the behavior of the circuit found in HW 10.6-PL. Also, includes some advanced material for the students who have an interest (not required).
- **BJT REVIEW PROBLEMS video Part 3**
  - Includes solutions for Worksheet 9 and a problem on  $p-n-p$  transistor.

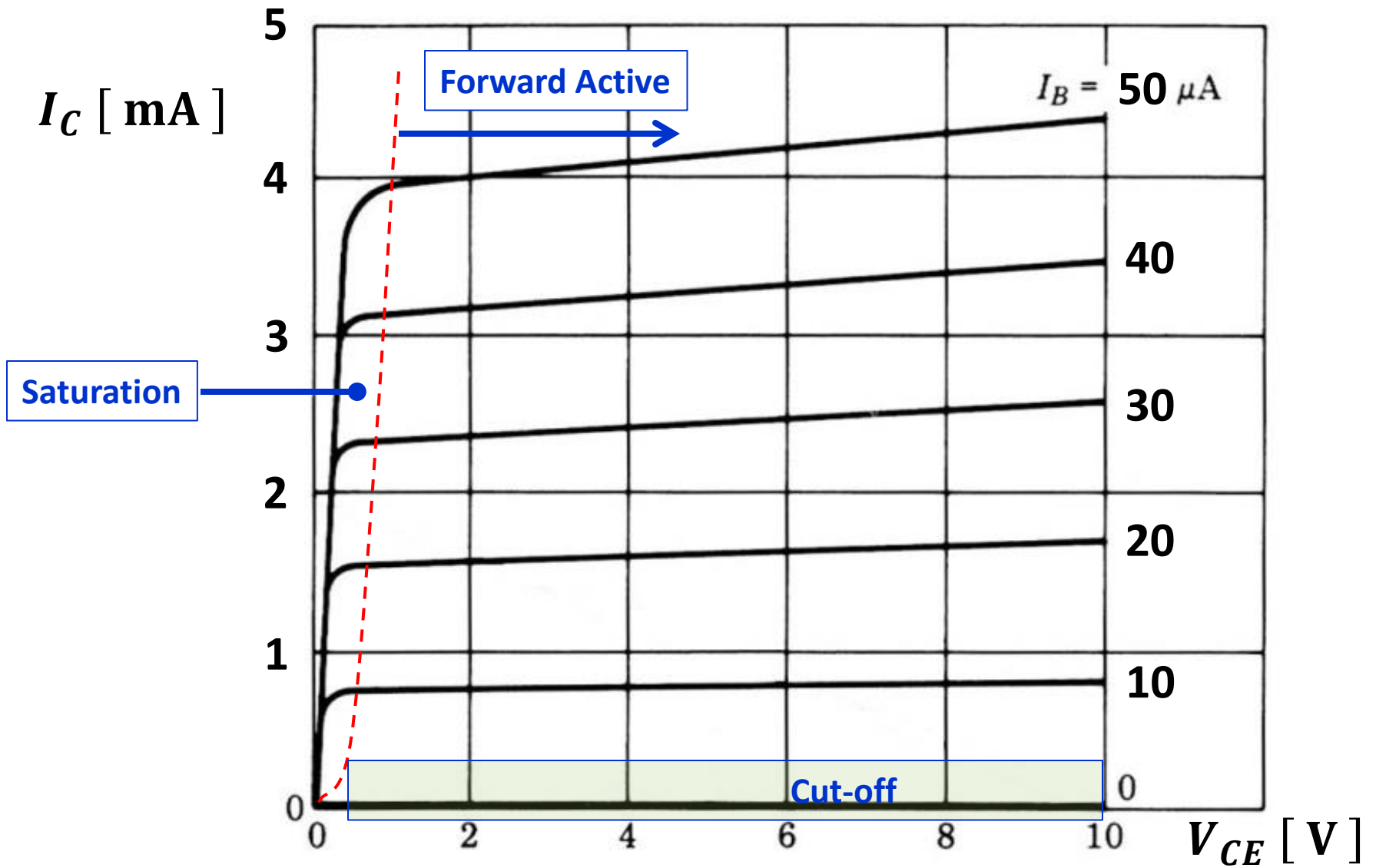
**Posted on Canvas in Module Week 11, Lecture 28**

# BJT $I$ - $V$ curves are measured on actual devices

Measurements are made by ramping the  $V_{CE}$  at specific values of base current  $I_B$



# BJT $I$ - $V$ curves

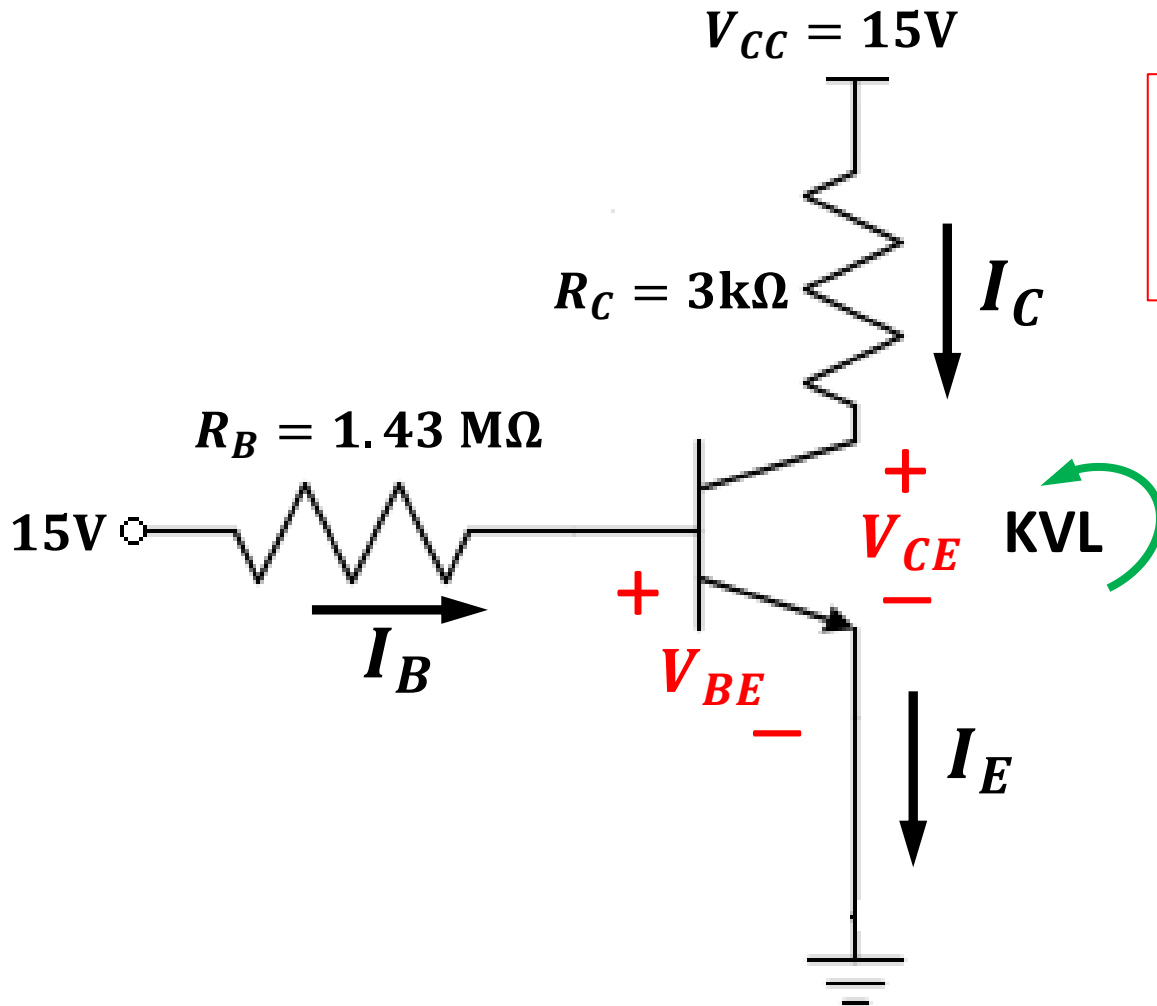


# Example of graphical use of BJT $I$ - $V$ curves

$$V_{BE(\text{on})} = 0.7\text{V}$$

$$\beta = 100$$

$$\boxed{\text{KVL}} \quad V_{CE} = V_{CC} - I_C R_C$$



Let's write  $I_C$  as a function of  $V_{CE}$

# Example of graphical use of BJT $I$ - $V$ curves

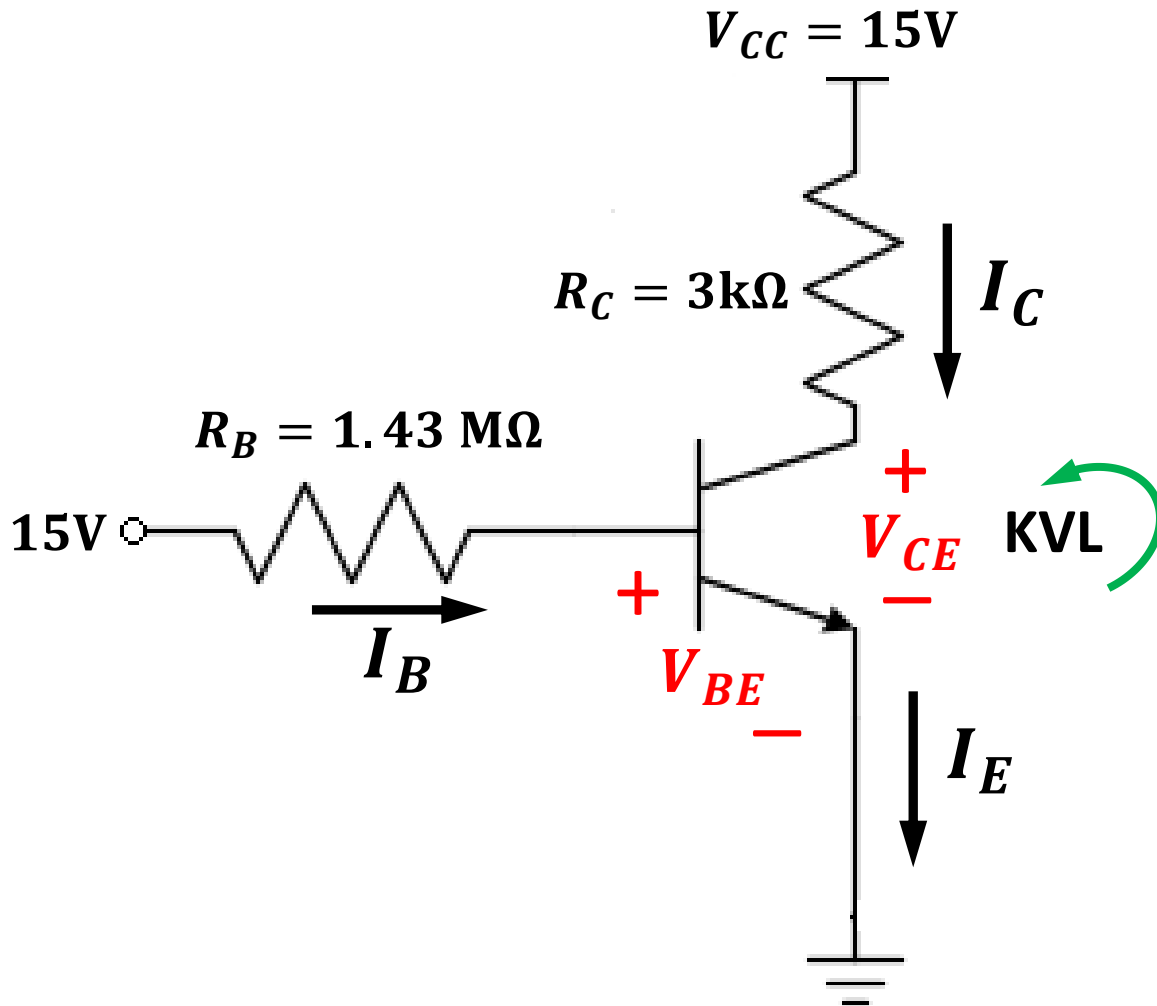
$$V_{BE(\text{on})} = 0.7\text{V}$$

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$$\boxed{\text{KVL}} \quad V_{CE} = V_{CC} - I_C R_C$$

$$I_C = \frac{V_{CC} - V_{CE}}{R_C}$$

$$I_C = \frac{15 - V_{CE}}{3\text{k}\Omega}$$





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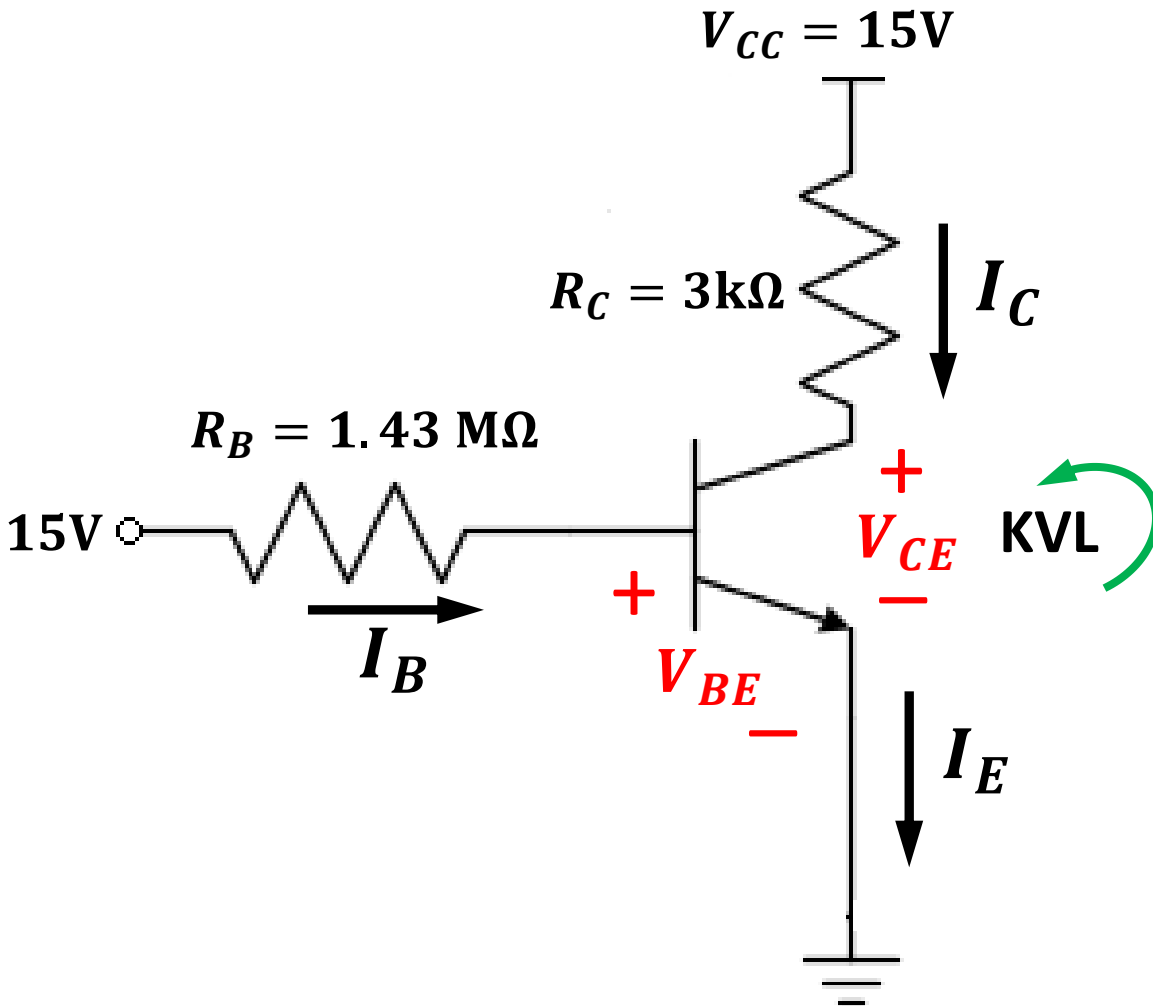
$$\boxed{\text{KVL}} \quad V_{CE} = V_{CC} - I_C R_C$$

$$I_C = \frac{V_{CC} - V_{CE}}{R_C}$$

$$I_C = \frac{15 - V_{CE}}{3\text{k}\Omega}$$

$$I_C = 5\text{mA} - \frac{V_{CE}}{3\text{k}\Omega}$$

Equation of a straight line



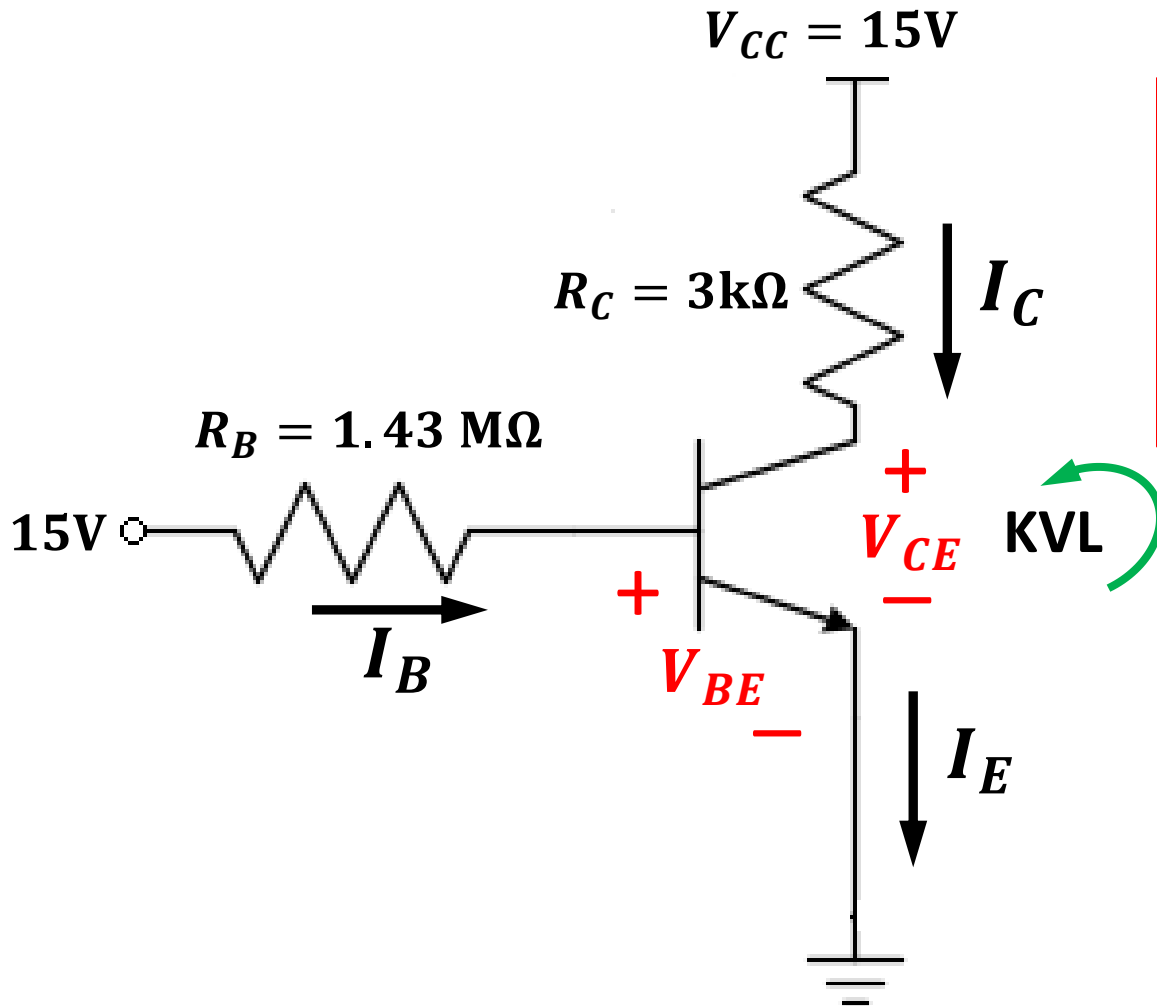
$V_{CE}$	$I_C$
0V	5mA
15V	0mA

# Example of graphical use of BJT $I$ - $V$ curves

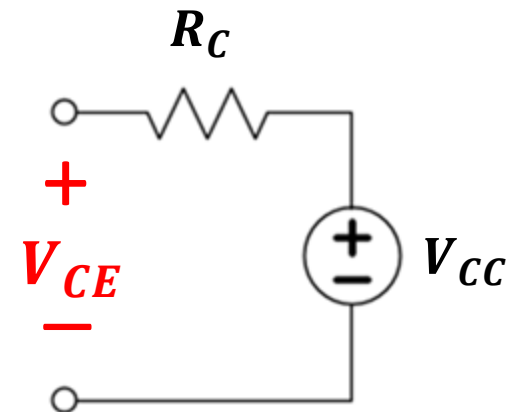
$$V_{BE(\text{on})} = 0.7\text{V}$$

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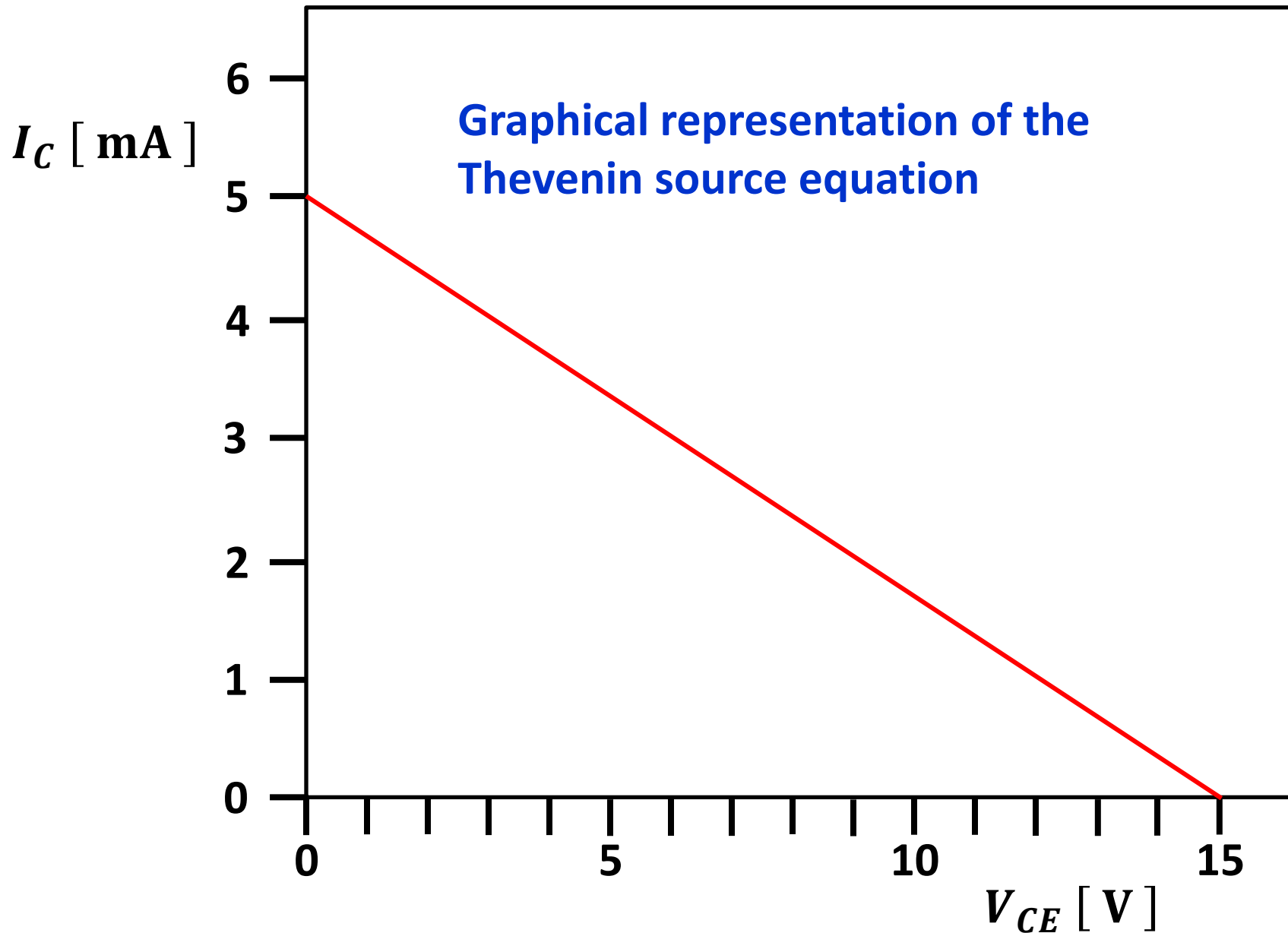
$$I_C = 5\text{mA} - \frac{V_{CE}}{3\text{k}\Omega}$$



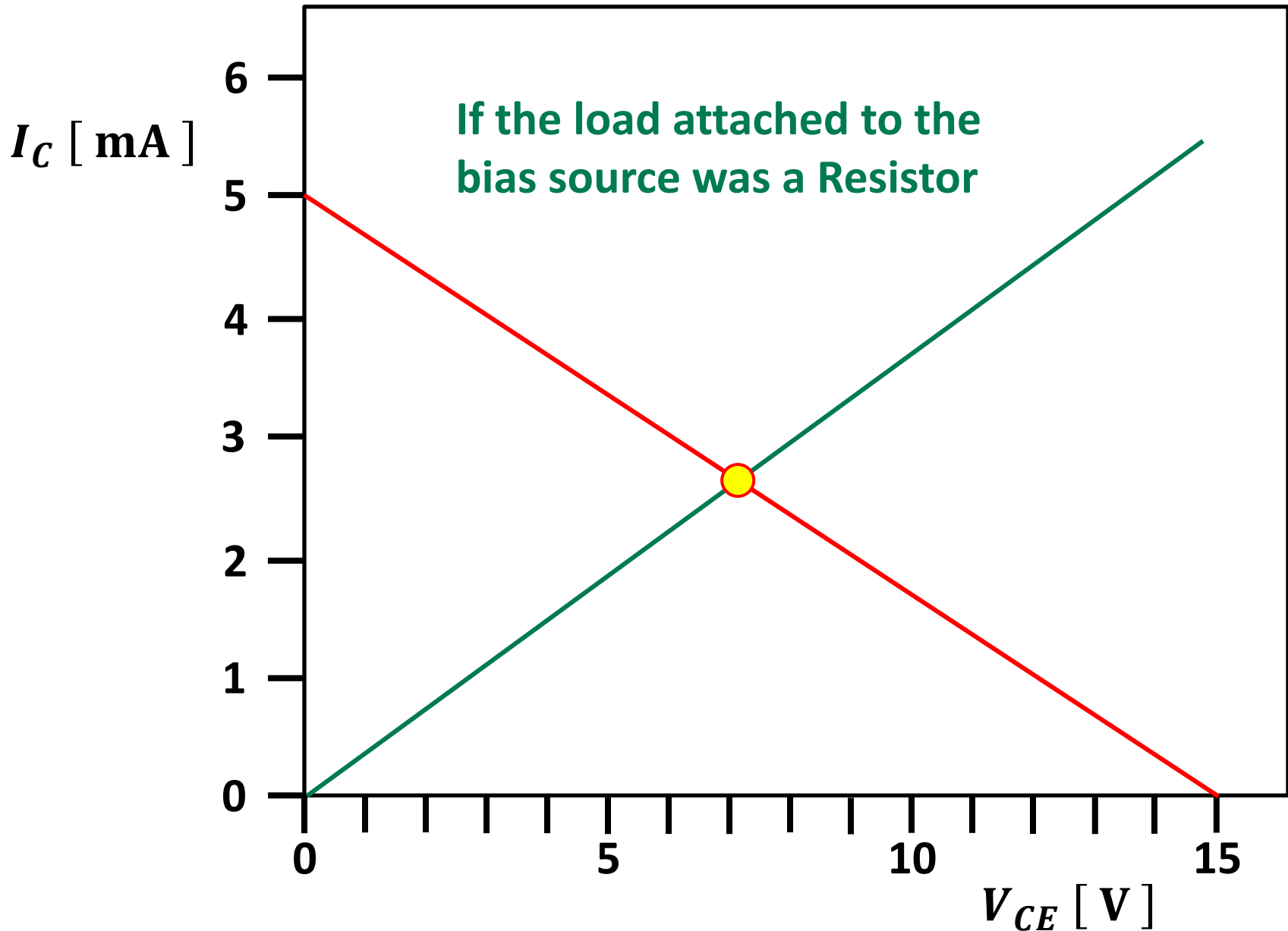
This equation just describes the collector biasing network as a Thevenin source. Here,  $V_{CE}$  and  $I_C$  depend on the behavior of the BJT, which is a non-linear load



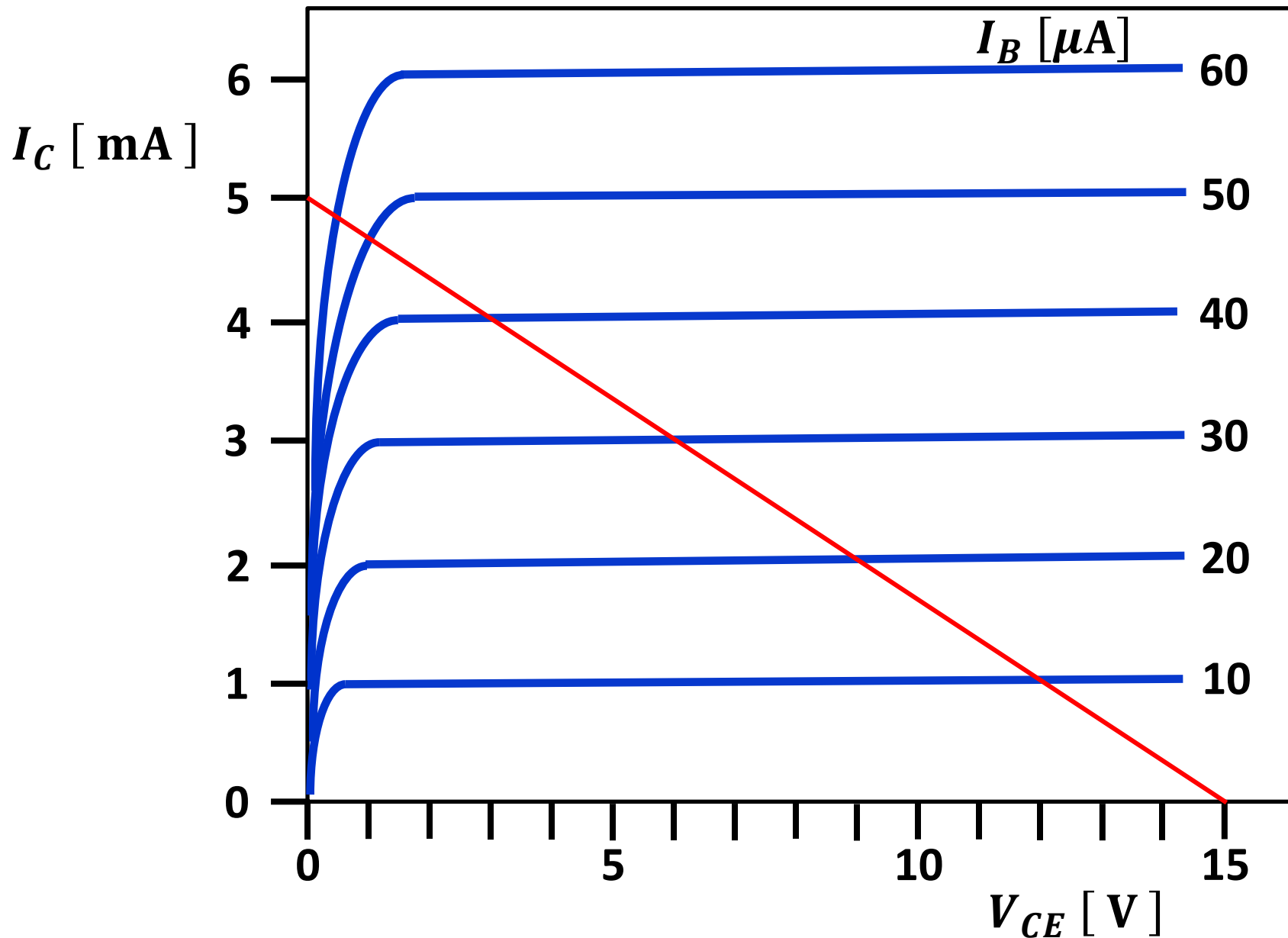
# Example of graphical use of BJT $I$ - $V$ curves



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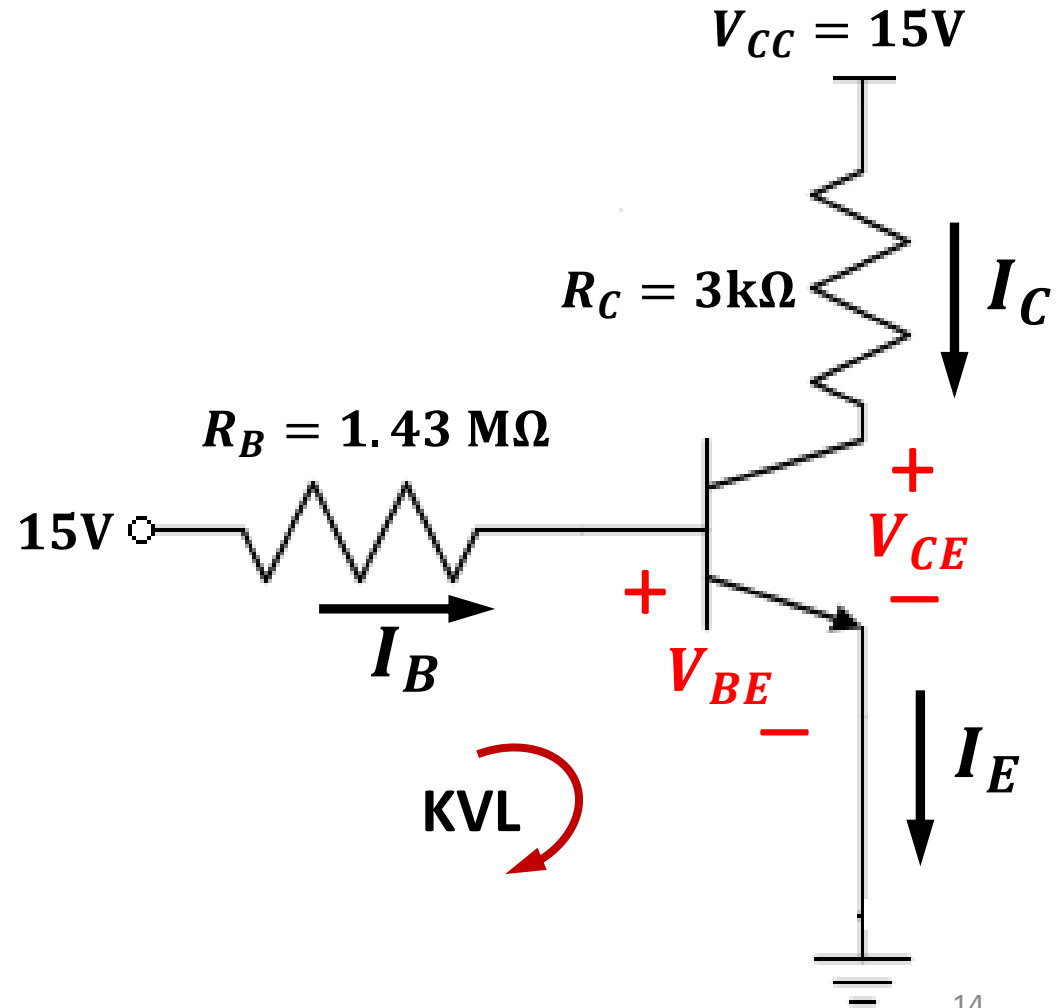


# Example of graphical use of BJT $I$ - $V$ curves

$$V_{BE}(\text{on}) = 0.7\text{V}$$

$$\beta = 100$$

Let's examine the Base circuit:



# Example of graphical use of BJT $I$ - $V$ curves

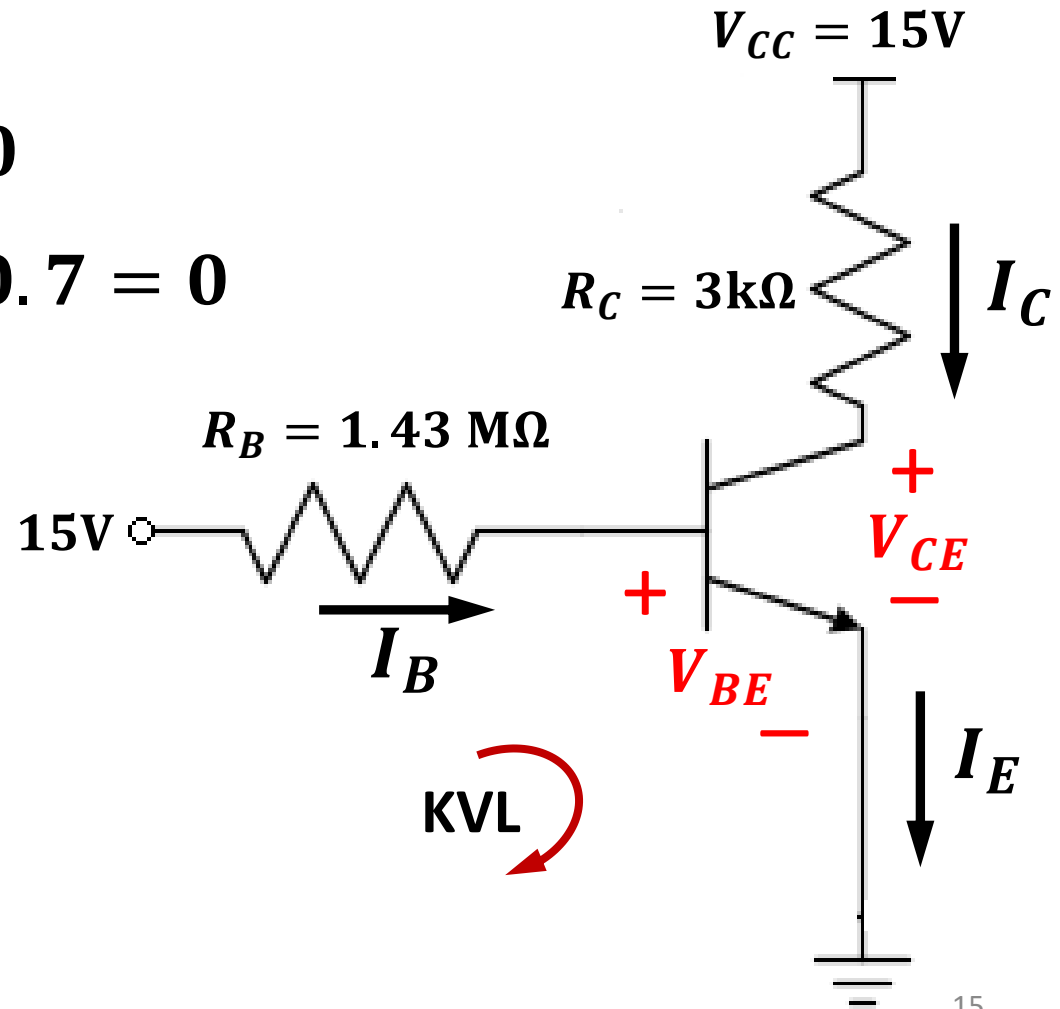
$$V_{BE}(\text{on}) = 0.7\text{V}$$

$$\beta = 100$$

Let's examine the Base circuit:

$$-15 + I_B R_B + V_{BE} = 0$$

$$-15 + 1.43\text{M} \times I_B + 0.7 = 0$$



# Example of graphical use of BJT $I$ - $V$ curves

$$V_{BE}(\text{on}) = 0.7\text{V}$$

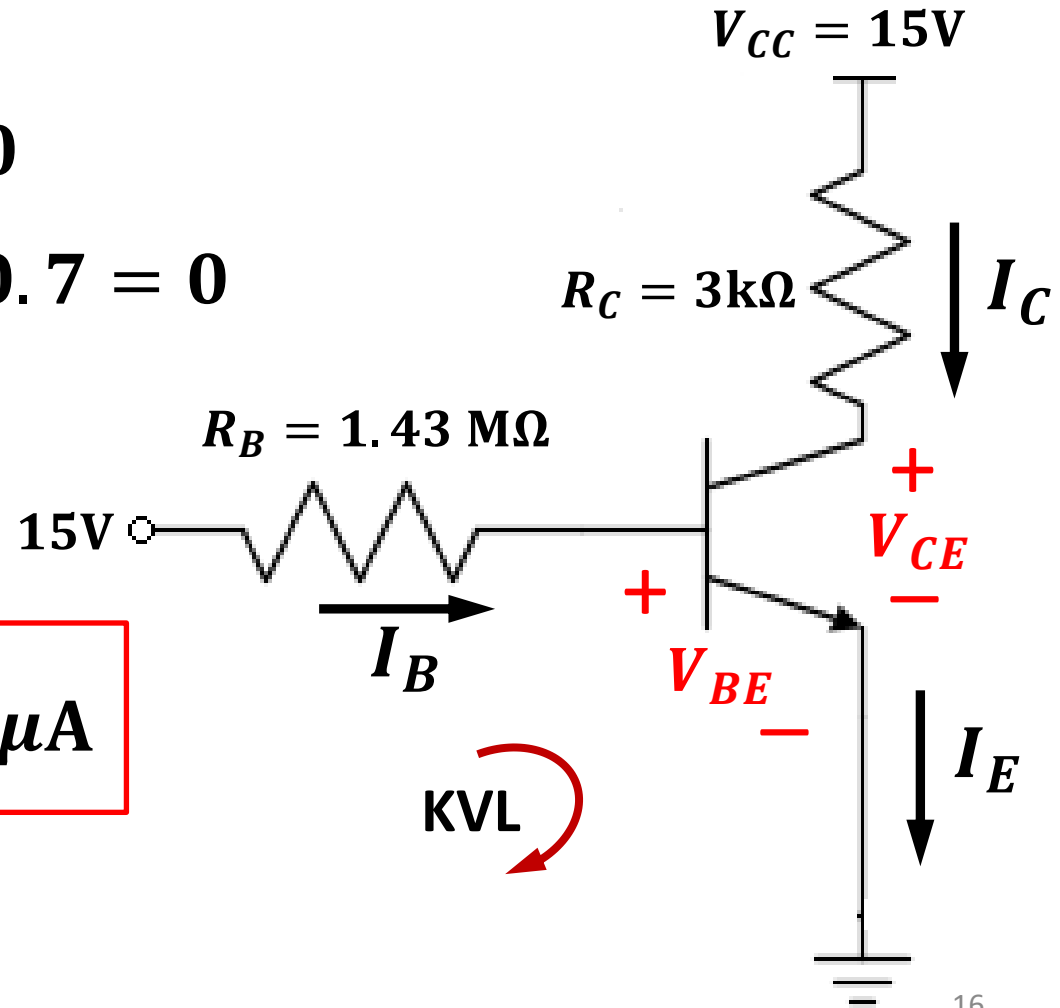
$$\beta = 100$$

Let's examine the Base circuit:

$$-15 + I_B R_B + V_{BE} = 0$$

$$-15 + 1.43\text{M} \times I_B + 0.7 = 0$$

$$I_B = \frac{14.3}{1.43 \times 10^6} = 10\mu\text{A}$$





# Example of graphical use of BJT $I$ - $V$ curves

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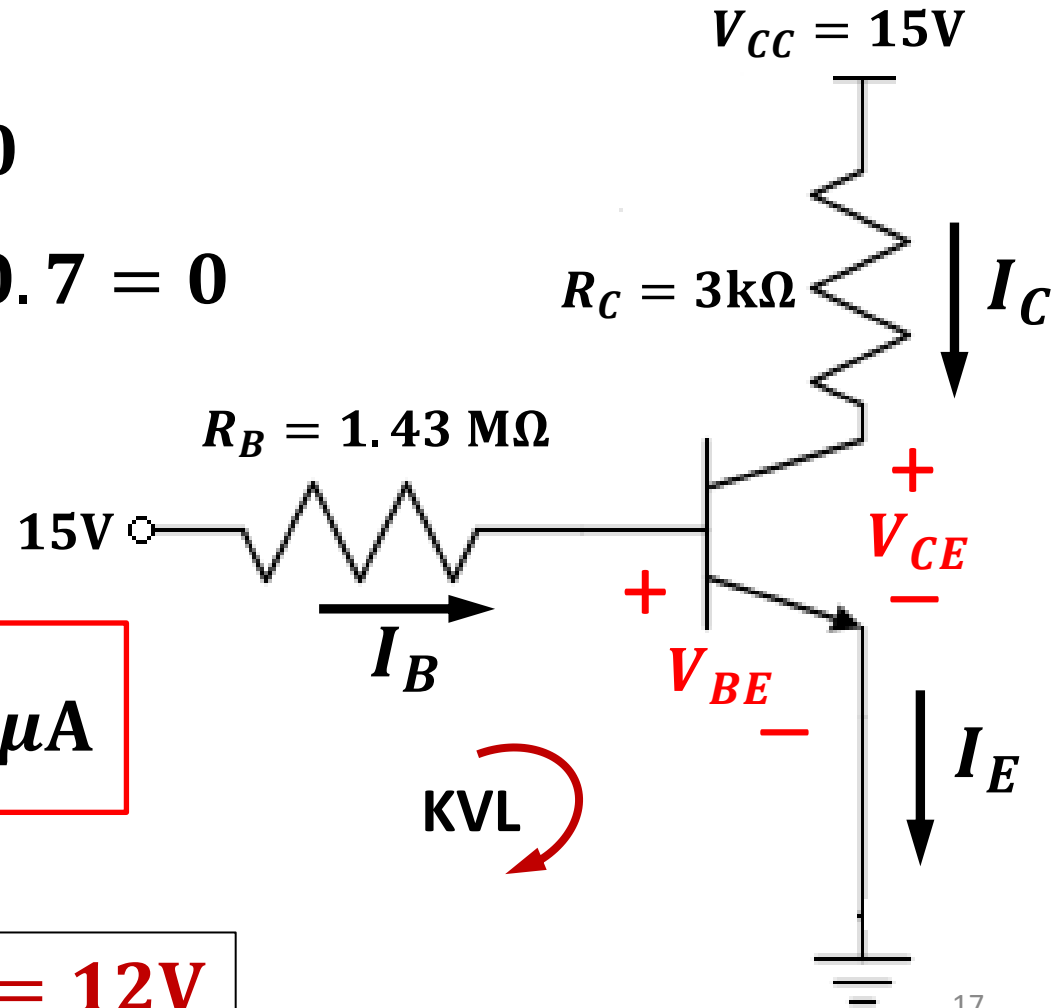
$$-15 + 1.43\text{M} \times I_B + 0.7 = 0$$

$$I_B = \frac{14.3}{1.43 \times 10^6} = 10\mu\text{A}$$

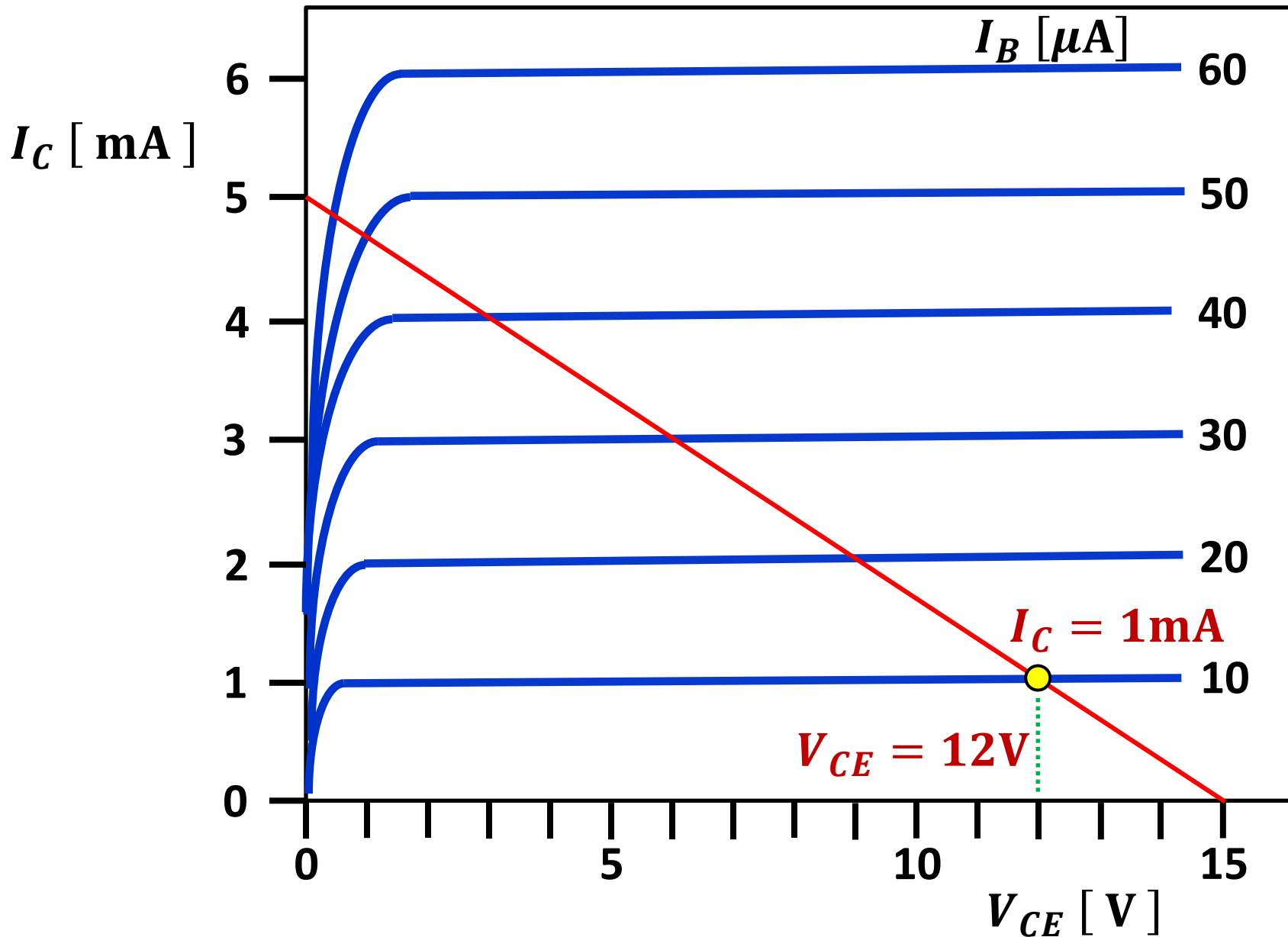
From the curves

$$I_C = 1\text{mA}$$

$$V_{CE} = 12\text{V}$$



# Example of graphical use of BJT $I$ - $V$ curves



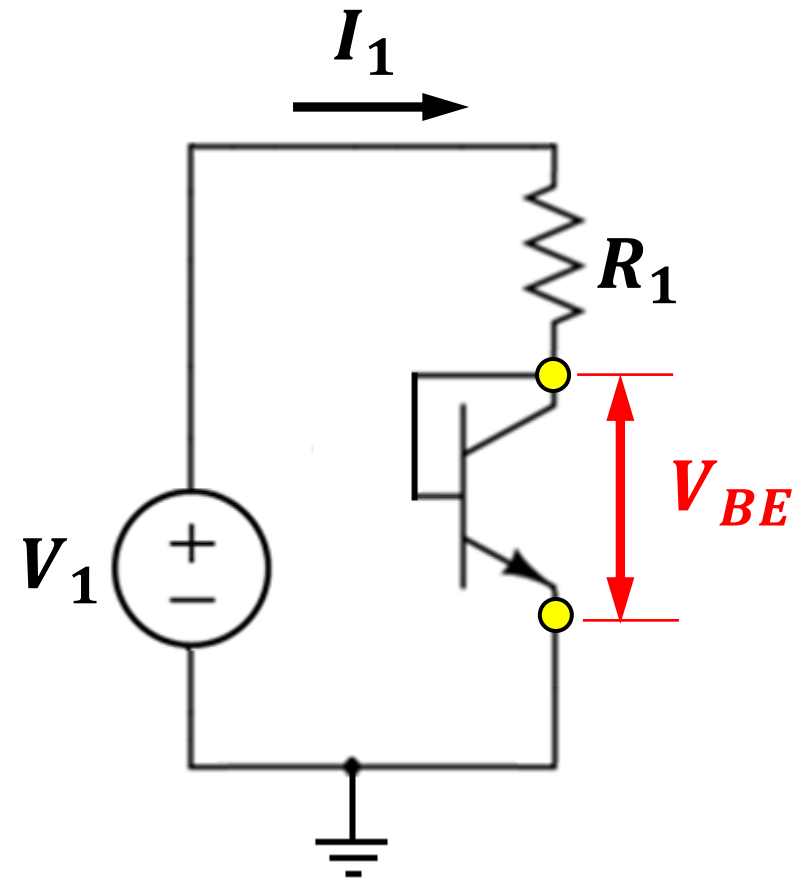
## BJT wired as a diode

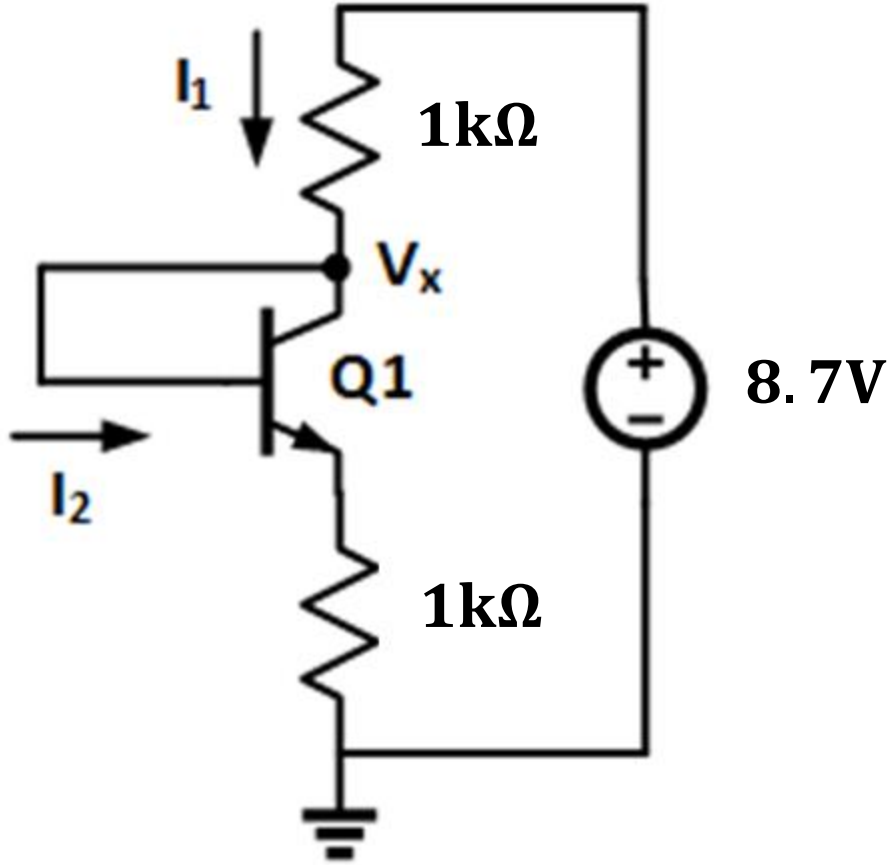
$$-V_1 + R_1 I_1 + V_{BE} = 0$$

$$I_1 = \frac{V_1 - V_{BE}}{R_1}$$

As long as  $V_1 > V_{BE}(\text{on})$ , the BJT is in Forward-Active mode.

BJT's wired as in the diagram, are often adopted in integrated circuits, to obtain ultra-low leakage diodes and for design of circuits which are temperature compensating.





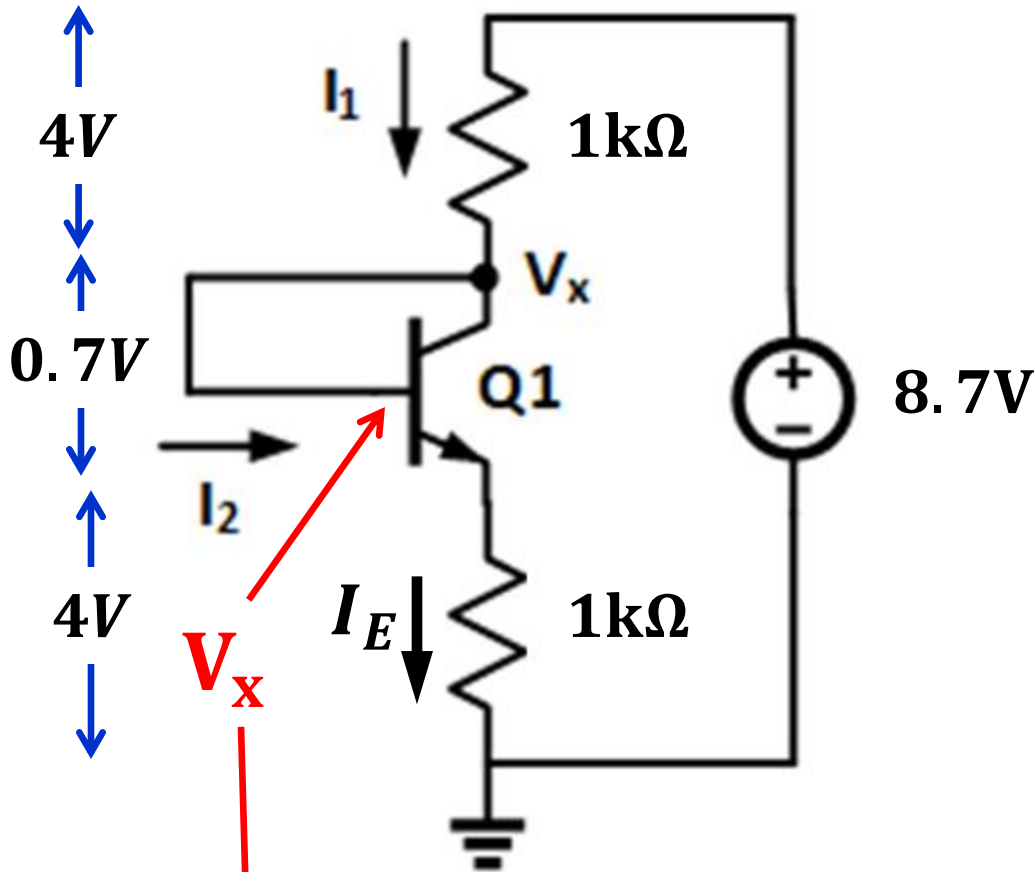
$$\beta = 100$$
$$V_{BE}(on) = 0.7V$$
$$V_{CE}(sat) = 0.2V$$

$$\beta = 100$$

$$V_{BE}(on) = 0.7V$$

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Assume: BJT ON



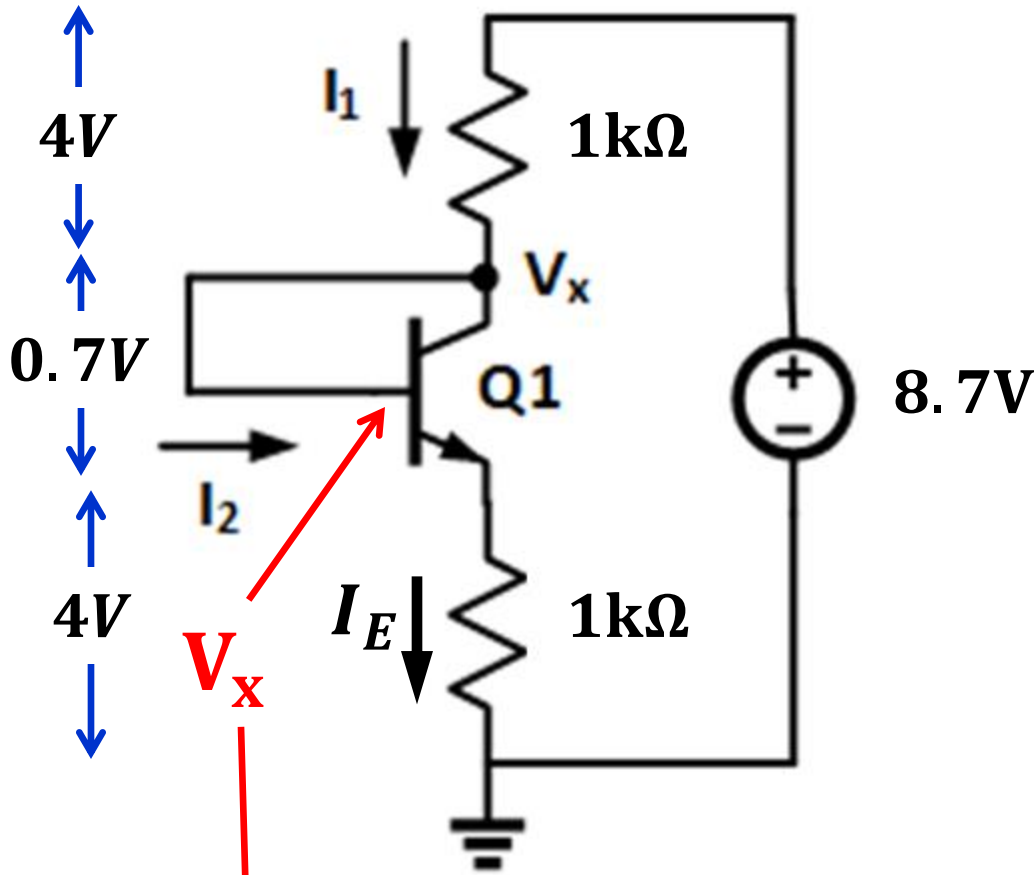
$$V_{BE} = V_{CE} = 0.7V$$

$$V_x = V_{CE} + 4V = 4.7V$$

$$\beta = 100$$

$$V_{BE}(on) = 0.7V$$

$$V_{CE}(sat) = 0.2V$$



Assume: BJT ON

$$I_1 = I_C + I_2$$
$$= I_C + I_B$$

$$I_1 = I_E$$

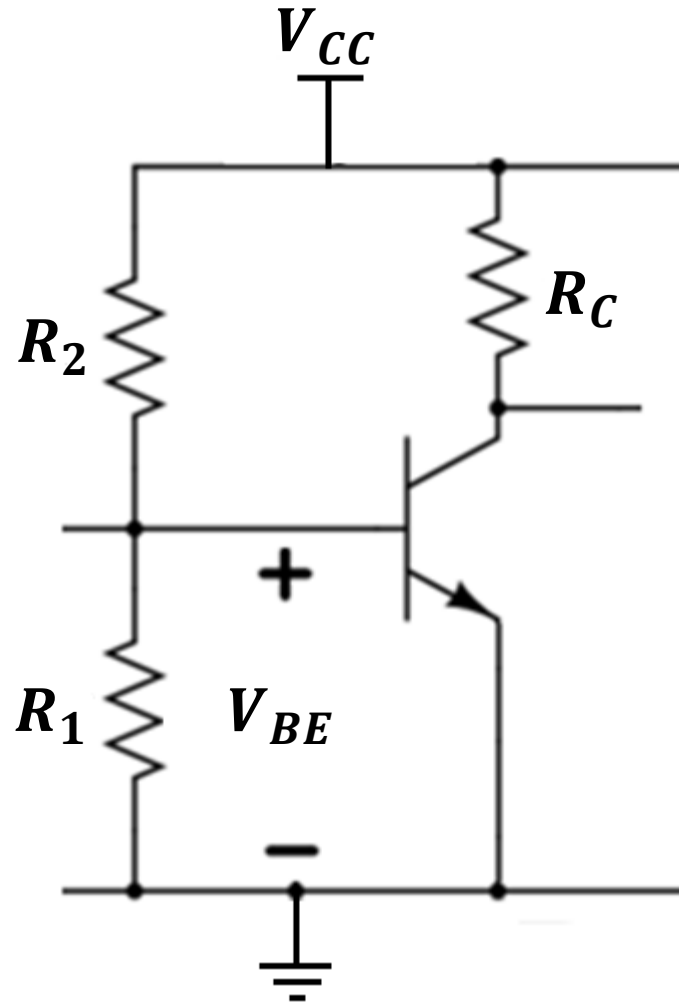
$$I_1 = 1k\Omega \times 4V$$
$$= 4mA$$

$$I_E = 1k\Omega \times 4V$$
$$= 4mA$$

$$V_{BE} = V_{CE} = 0.7V$$

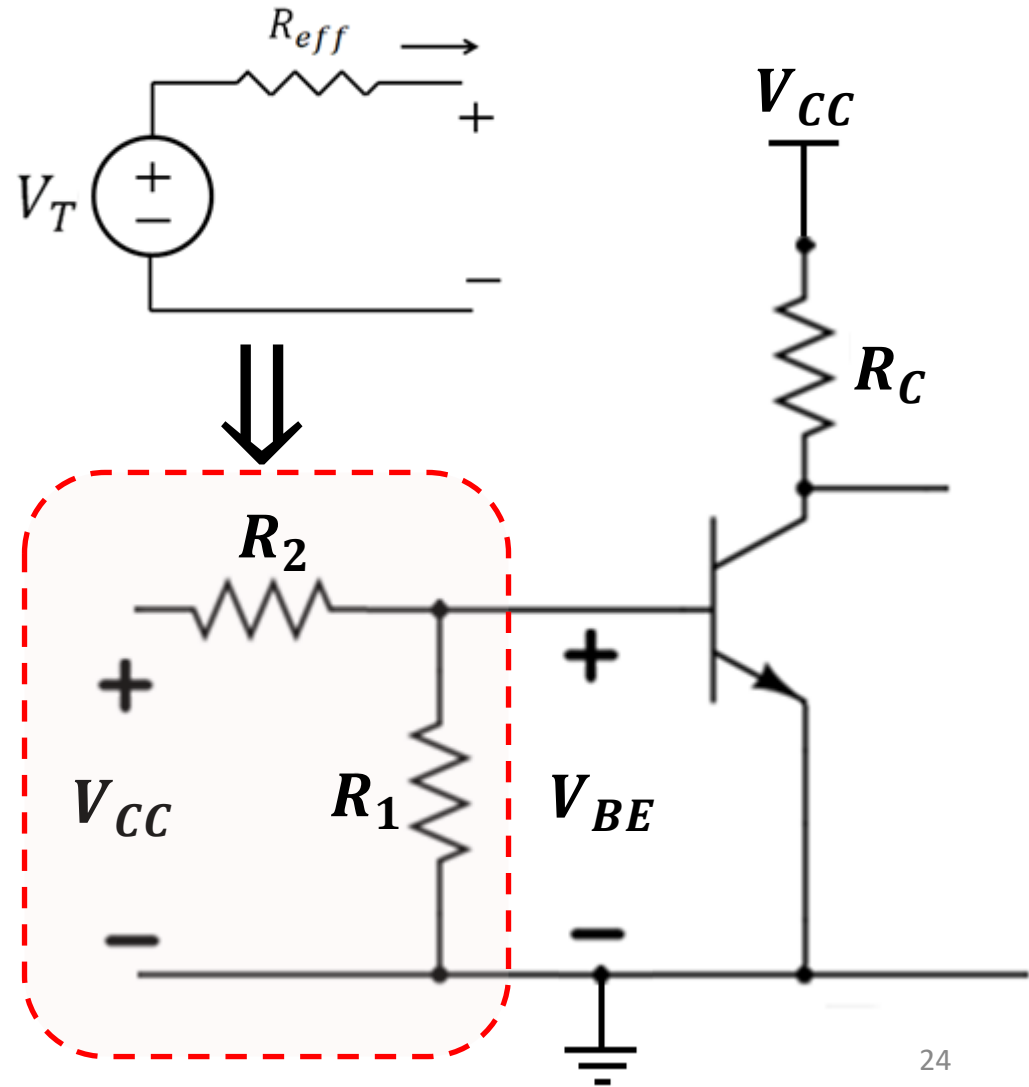
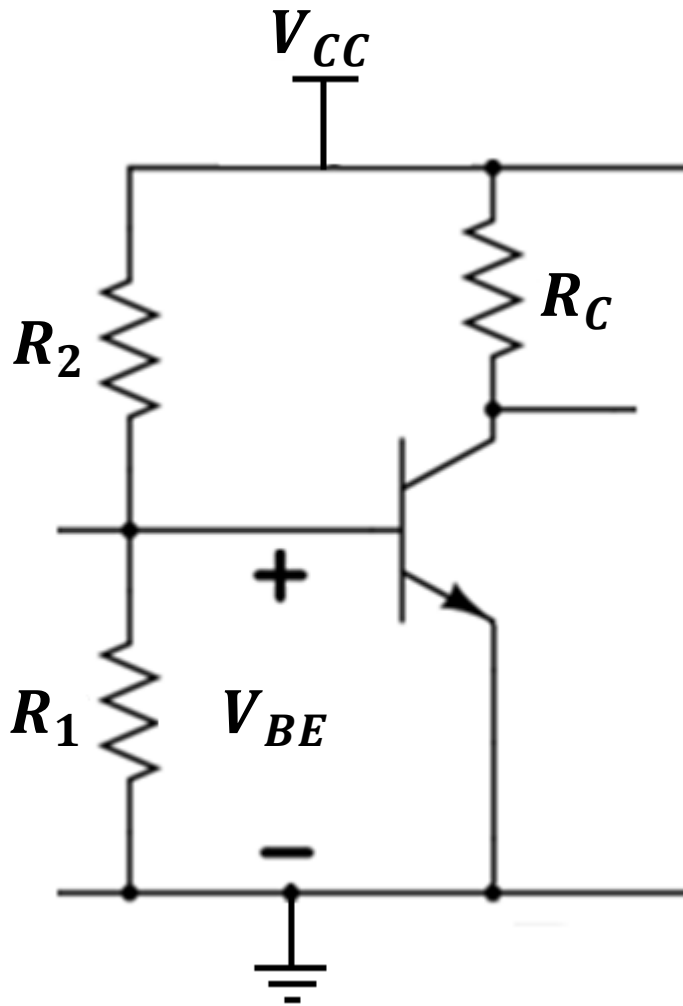
$$V_x = V_{CE} + 4V = 4.7V$$

# BJT Single battery bias



$$R_{eff} = R_1 // R_2$$

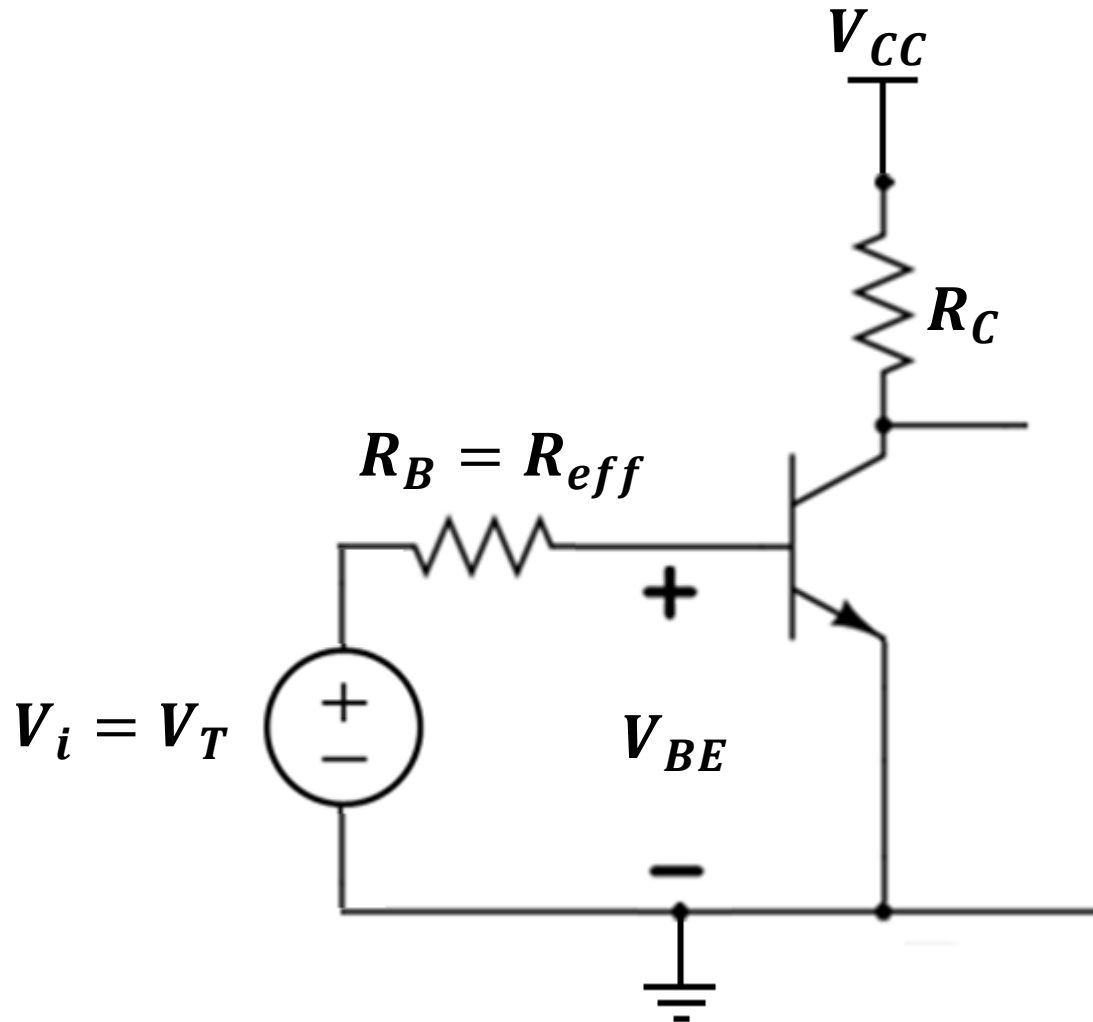
$$V_T = V_{CC} \frac{R_1}{R_1 + R_2}$$





$$R_{eff} = R_1 // R_2$$

$$V_T = V_{CC} \frac{R_1}{R_1 + R_2}$$

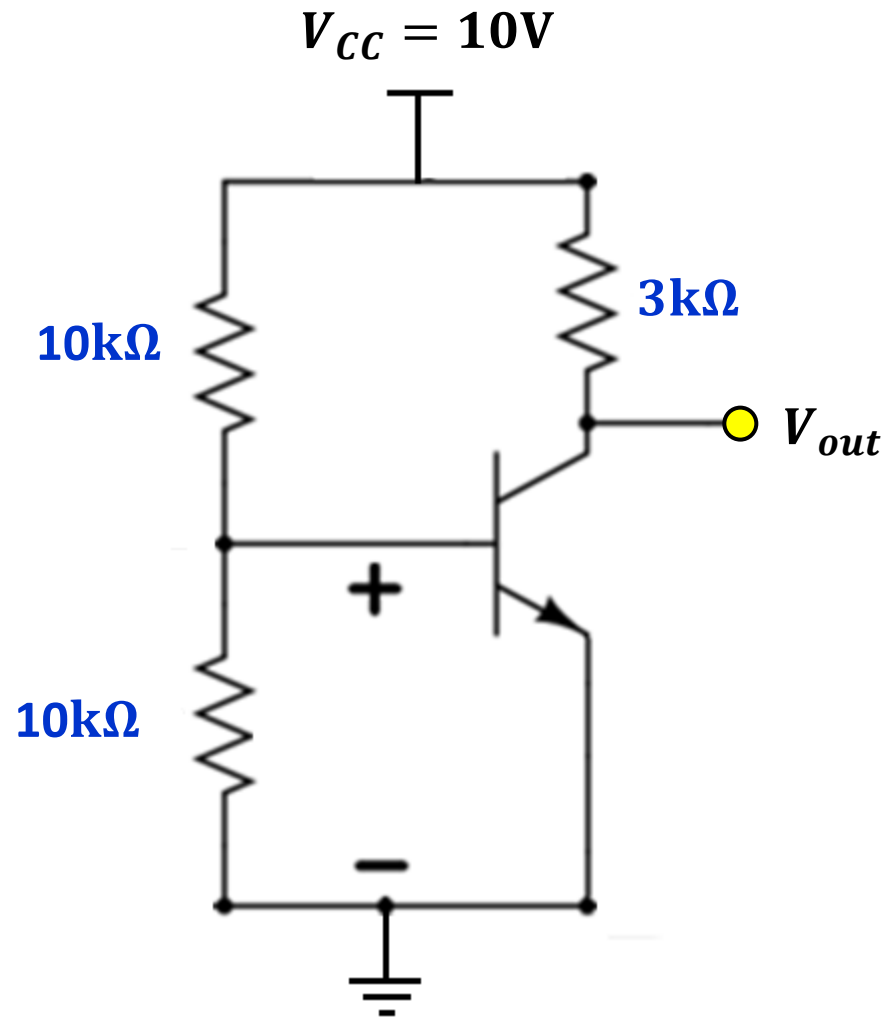


## BJT Single Battery Bias Example

$$V_{BE}(\text{on}) = 0.7\text{V}$$

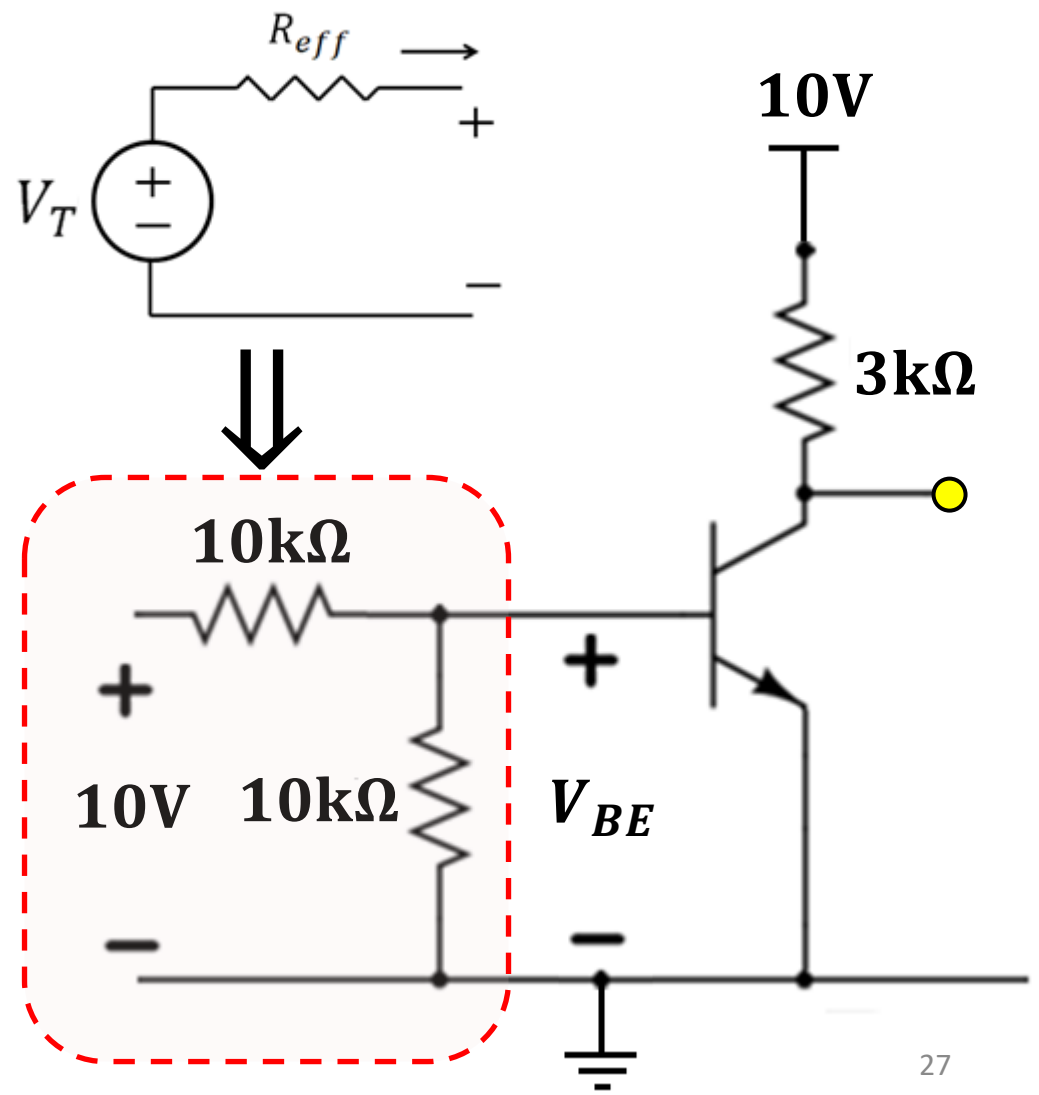
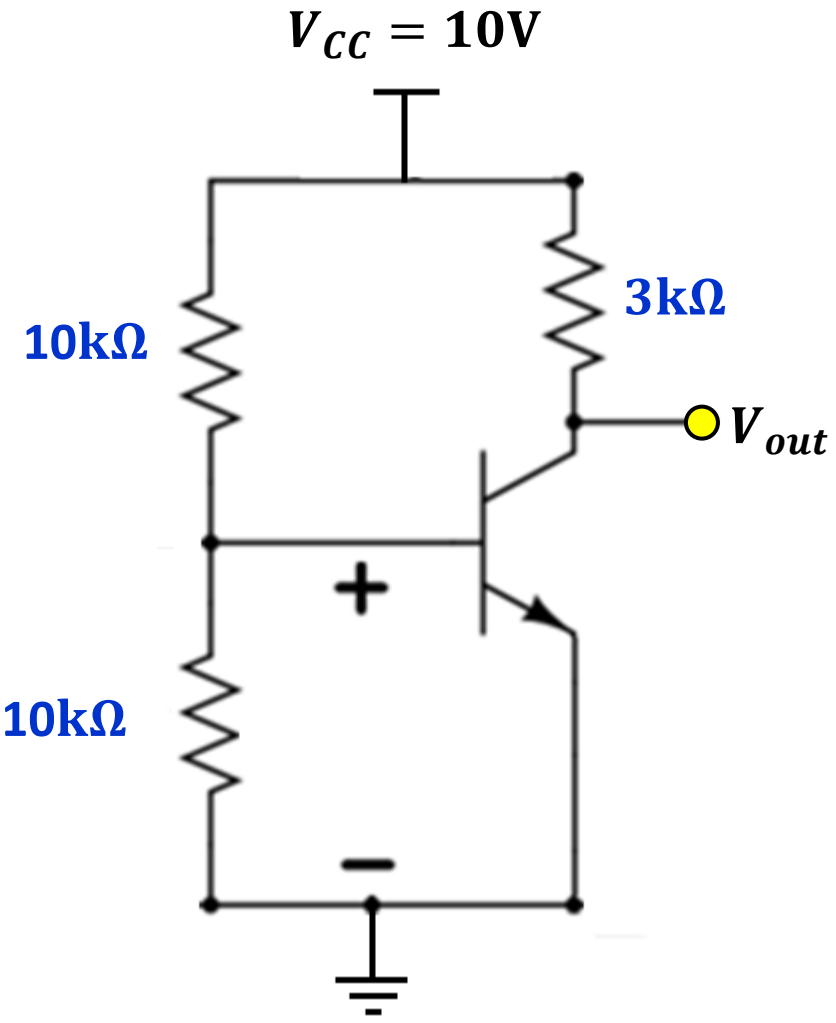
$$V_{CE}(\text{sat}) = 0.2\text{V}$$

$$\beta = 5$$



$$R_{eff} = R_1 // R_2 = 5k\Omega$$

$$V_T = 10 \frac{10k\Omega}{10k\Omega + 10k\Omega} = 5V$$



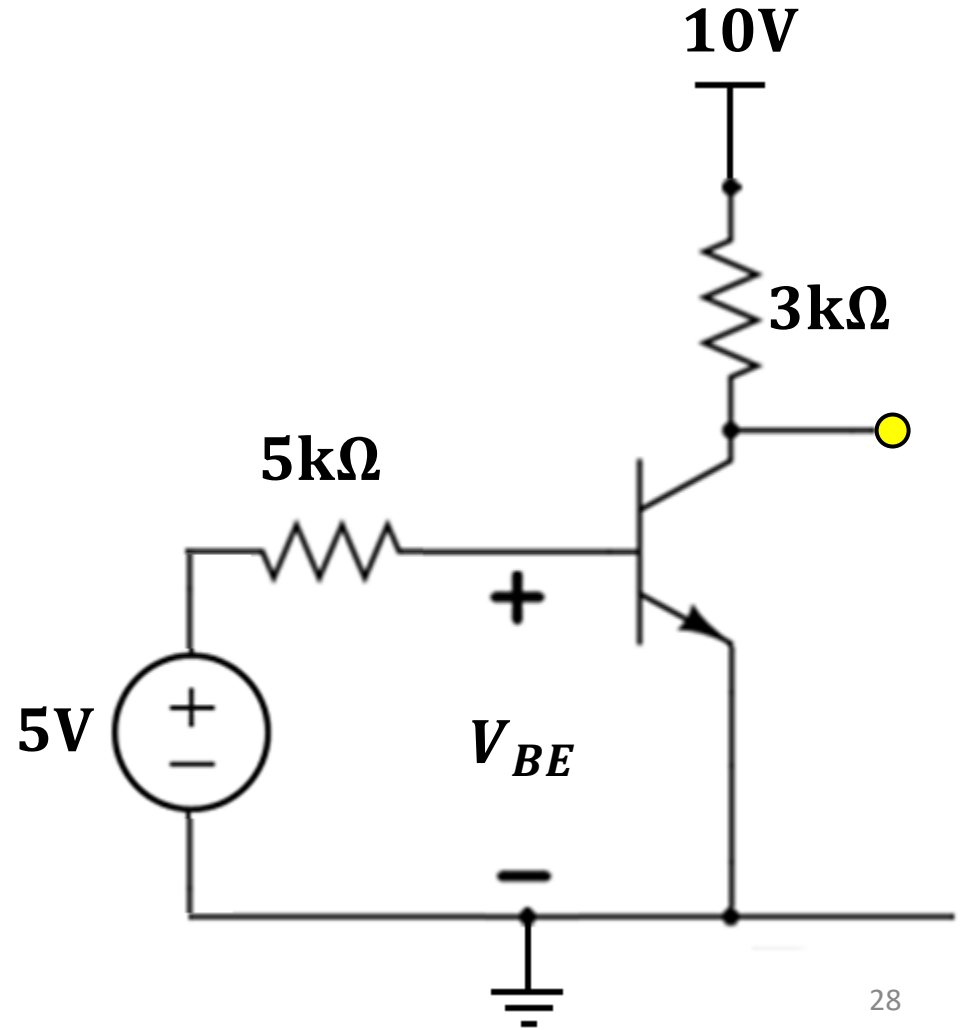
Assume Forward-Active Mode  $\beta = 5$

$$V_i = R_B I_B + V_{BE}$$

$$5 = 5k I_B + 0.7$$

$$I_B = \frac{4.3}{5k}$$

$$I_B = 0.86 \text{ mA}$$



Assume Forward-Active Mode  $\beta = 5$

$$V_i = R_B I_B + V_{BE}$$

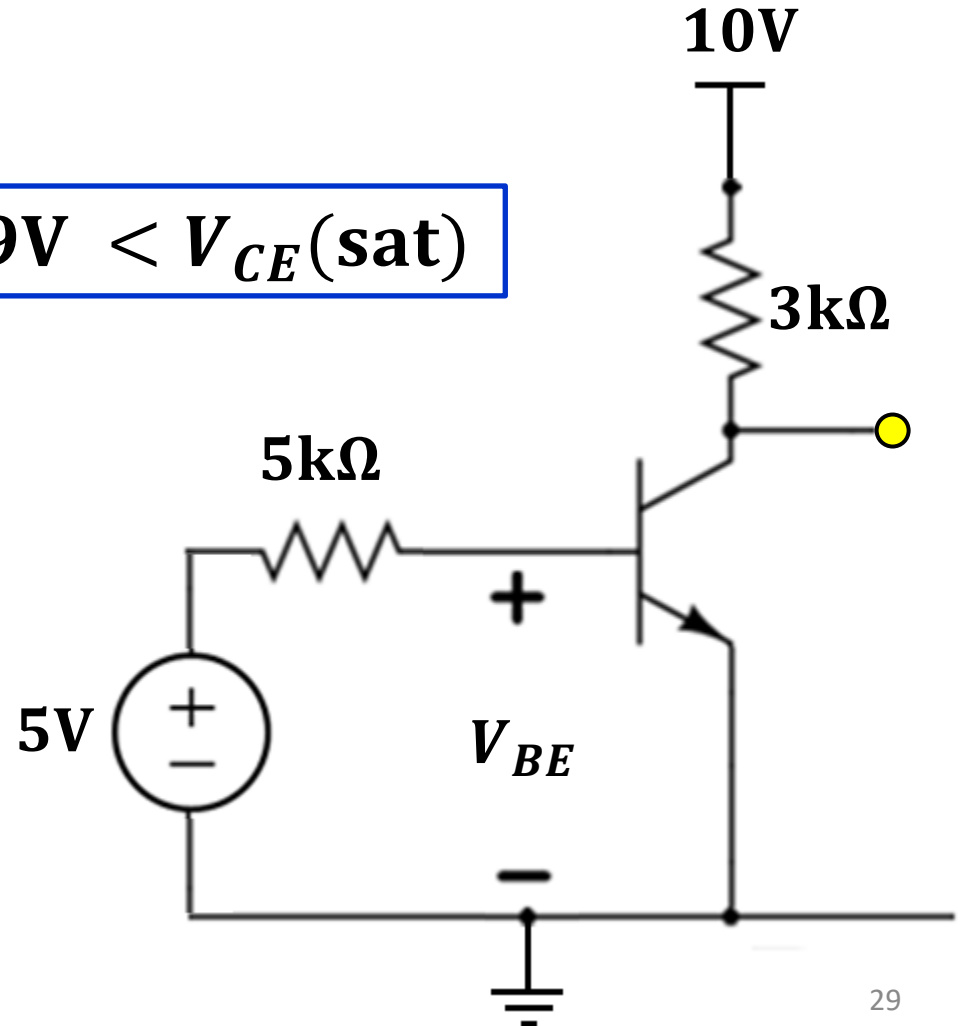
$$5 = 5k I_B + 0.7$$

$$I_B = \frac{4.3}{5k}$$

$$I_B = 0.86 \text{ mA}$$

$$I_C = \beta I_B = 4.3 \text{ mA}$$

$$V_{CE} = V_{CC} - 3k I_C = -2.9 \text{ V} < V_{CE}(\text{sat})$$



Assume Forward-Active Mode  $\beta = 5$

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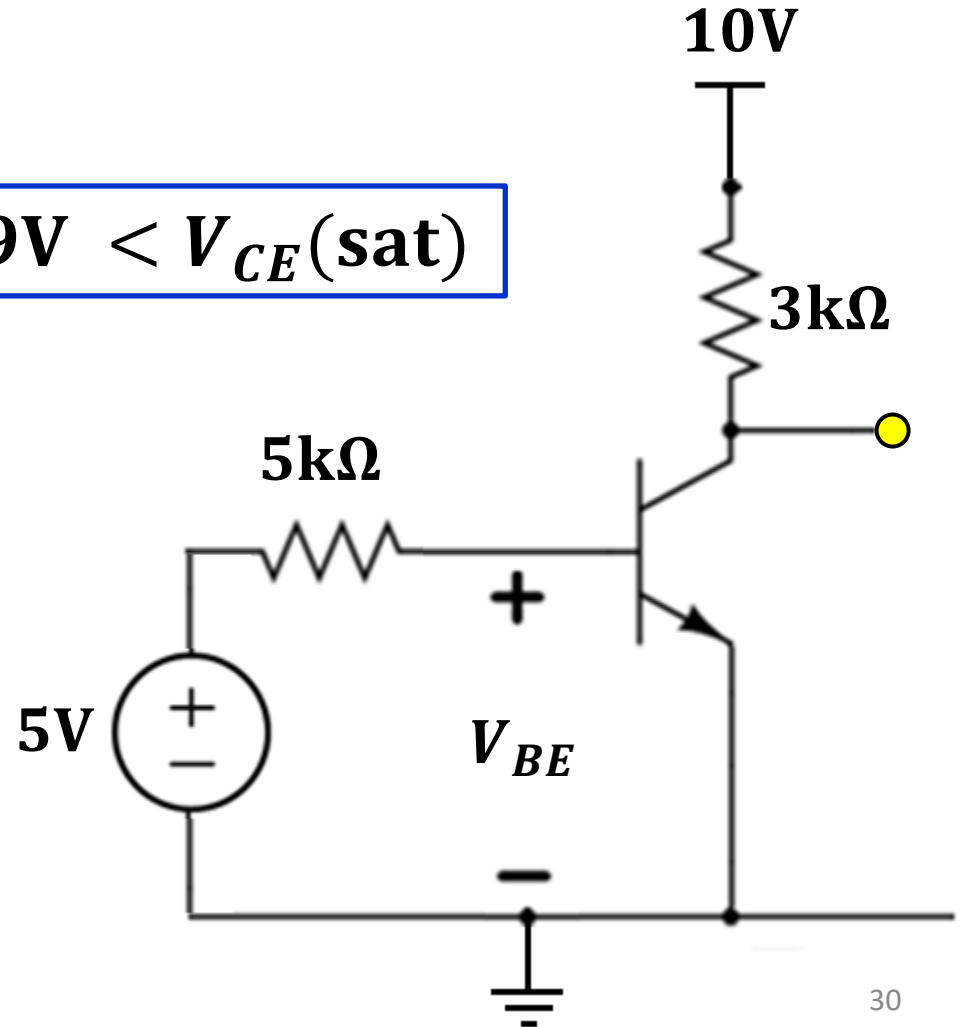
$$I_C = \beta I_B = 4.3 \text{ mA}$$

$$V_{CE} = V_{CC} - 3k I_C = -2.9 \text{ V} < V_{CE}(\text{sat})$$

**BJT is in saturation:**

$$I_C(\text{sat}) = \frac{10 - 0.2}{3k} = 3.2\bar{6} \text{ mA}$$

$$V_{CE} = V_{CE}(\text{sat}) = 0.2 \text{ V}$$



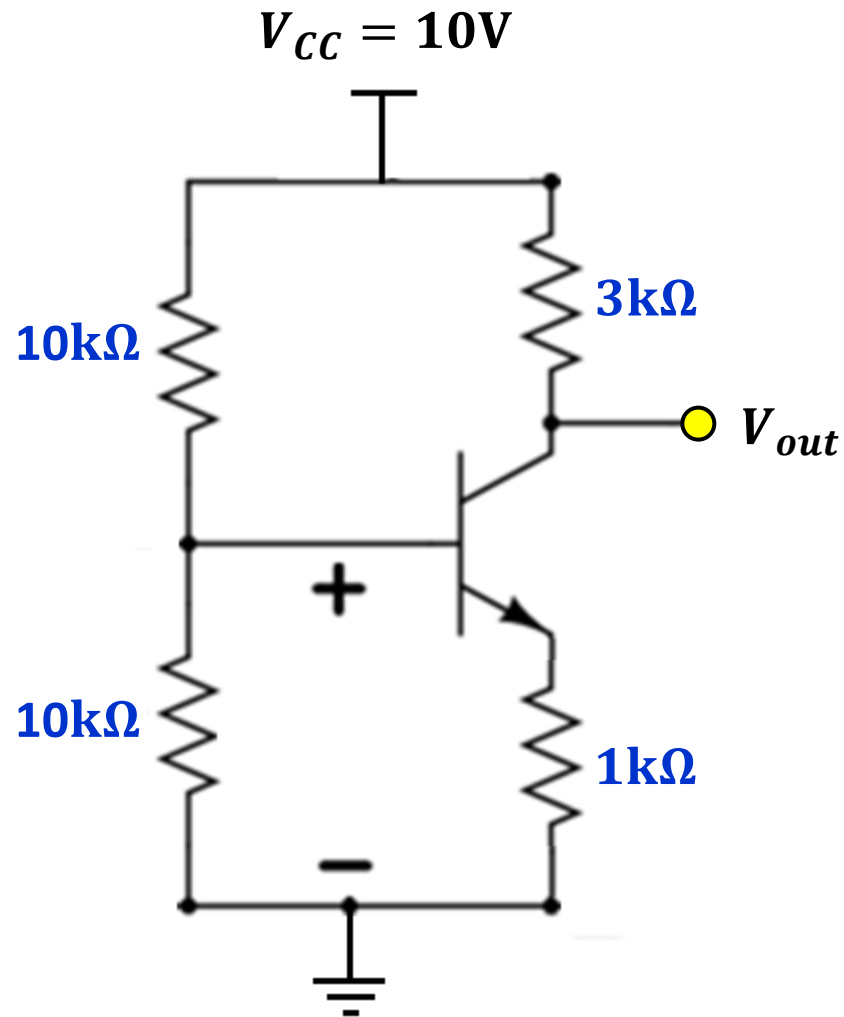
# BJT Single Battery Bias – Resistor on Emitter

$$V_{BE}(\text{on}) = 0.7\text{V}$$

$$V_{CE}(\text{sat}) = 0.2\text{V}$$

$$\beta = 5$$

Add Emitter Resistor



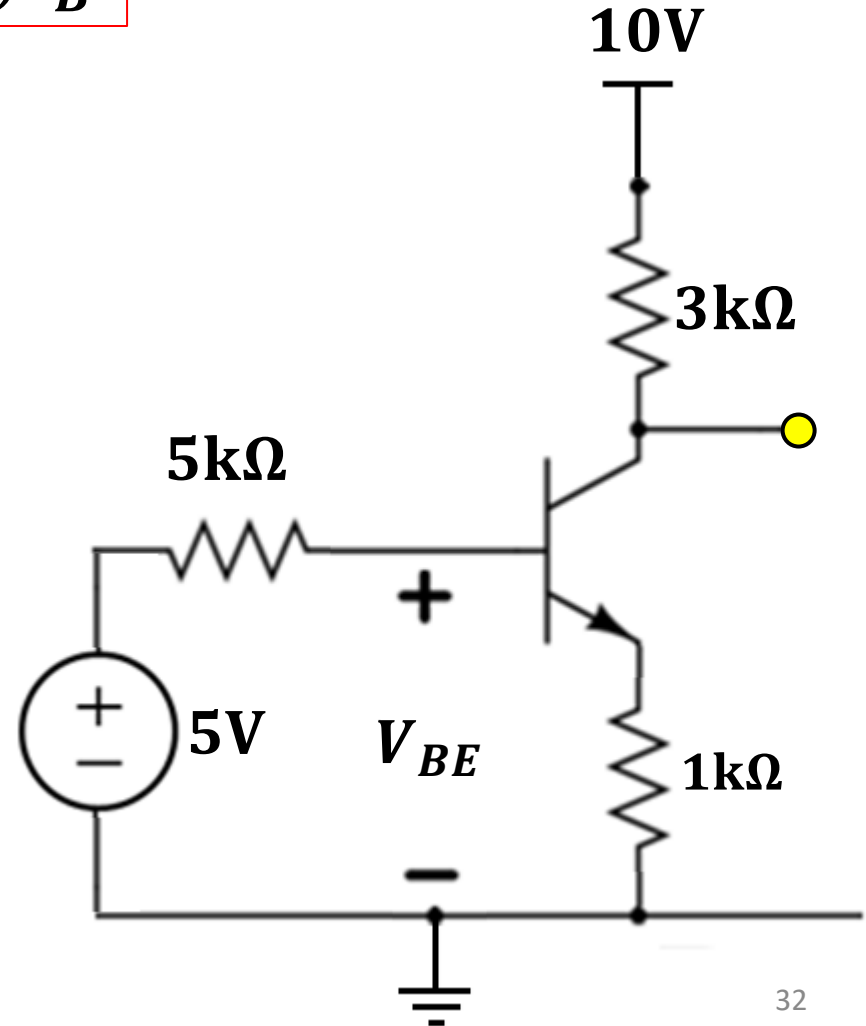
Assume Forward-Active Mode  $\beta = 5$

$$V_i = R_B I_B + V_{BE} + R_E I_E$$

$$5 = 5k I_B + 0.7 + 1k (\beta + 1) I_B$$

$$I_B = 0.391 \text{ mA}$$

Assumption is valid





Assume Forward-Active Mode  $\beta = 5$

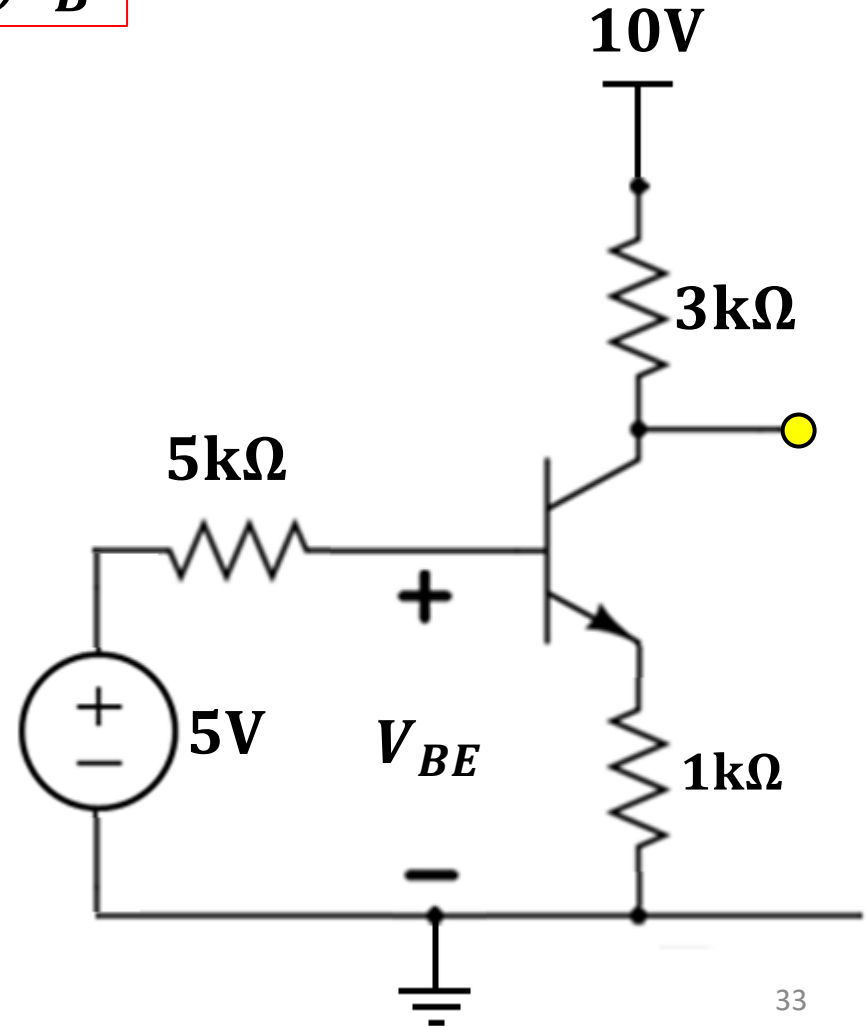
$$V_i = R_B I_B + V_{BE} + R_E I_E$$

$$5 = 5\text{k} I_B + 0.7 + 1\text{k} (\beta + 1) I_B$$

$$I_B = 0.391 \text{ mA}$$

$$I_C = \beta I_B = 1.955 \text{ mA}$$

$$I_E = (\beta + 1) I_B = 2.346 \text{ mA}$$



Assume Forward-Active Mode  $\beta = 5$

$$V_i = R_B I_B + V_{BE} + R_E I_E$$

$$5 = 5k I_B + 0.7 + 1k (\beta + 1) I_B$$

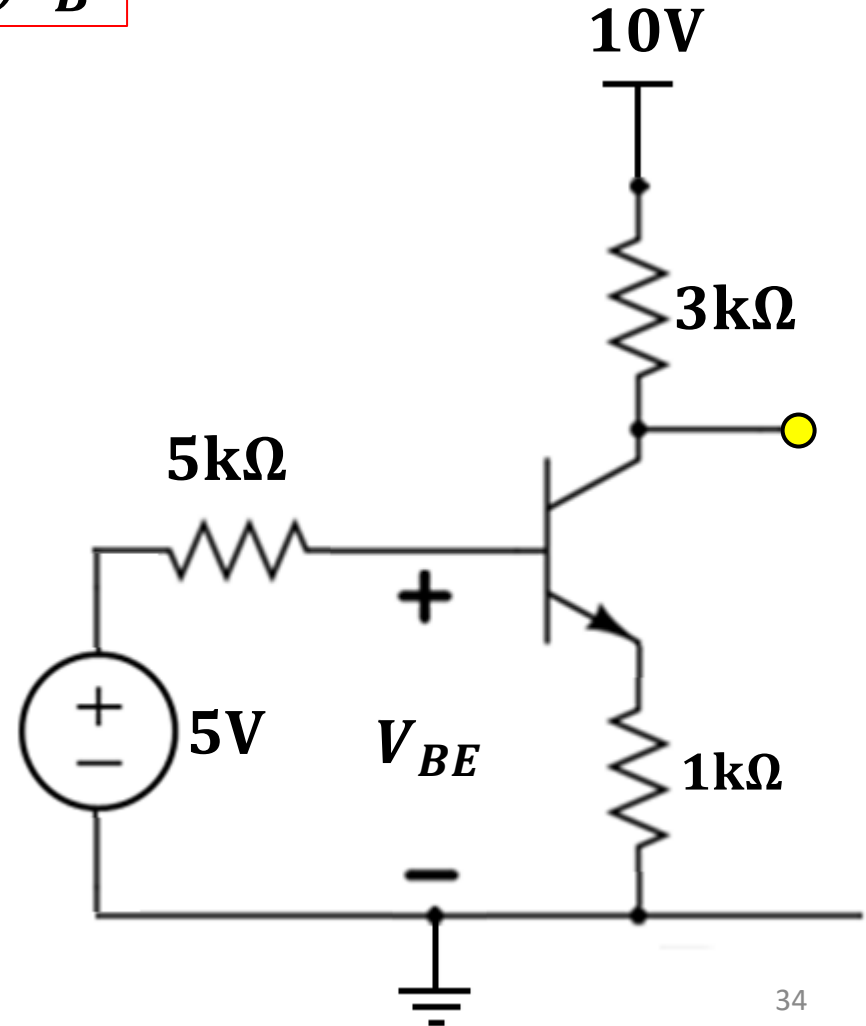
$$I_B = 0.391 \text{ mA}$$

$$I_C = \beta I_B = 1.955 \text{ mA}$$

$$I_E = (\beta + 1) I_B = 2.346 \text{ mA}$$

$$\begin{aligned} V_{CE} &= 10 - 3k I_C - 1k I_E \\ &= 1.789 \text{ V} > V_{CE}(\text{sat}) \end{aligned}$$

Assumption is valid

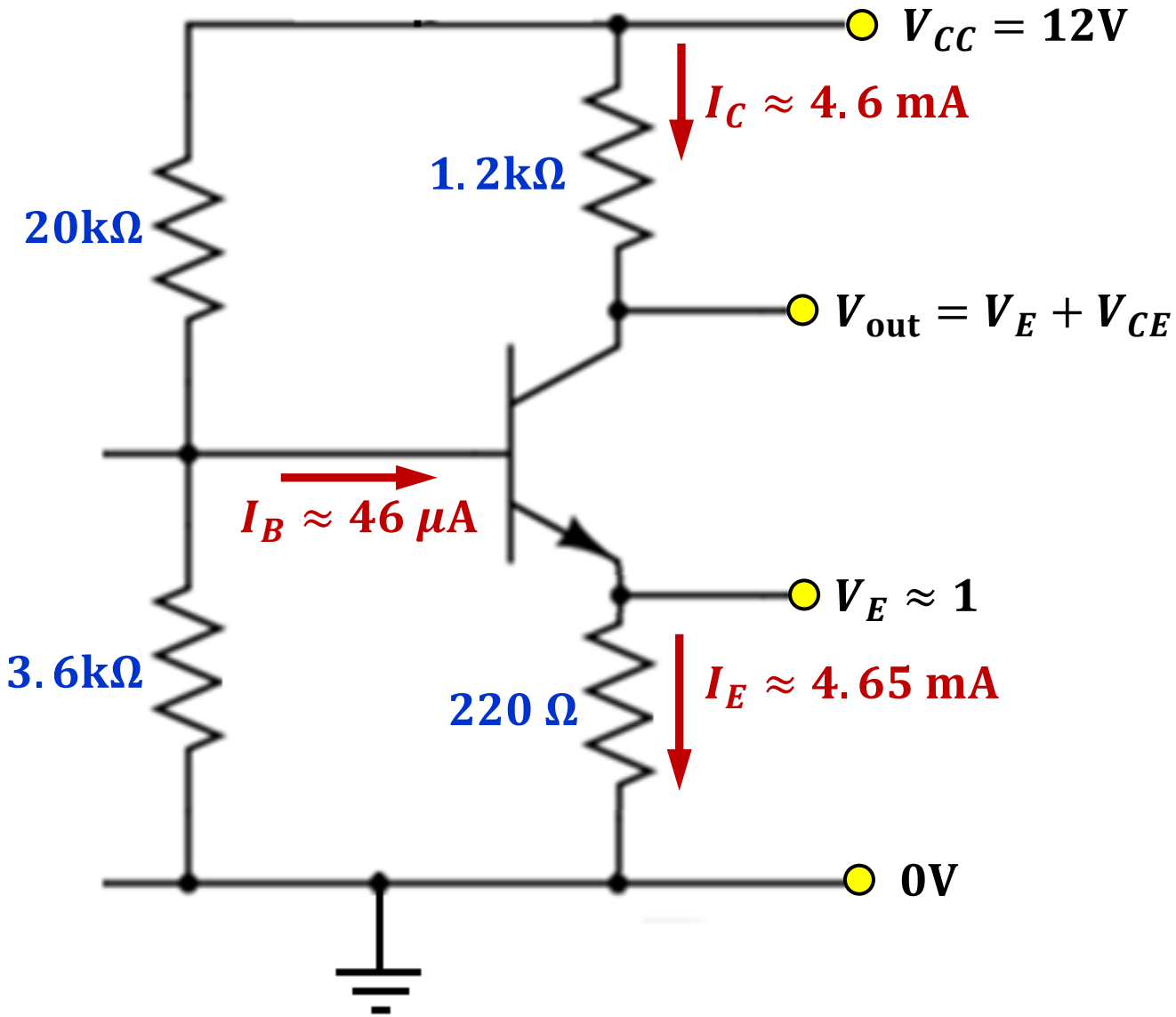


# BJT

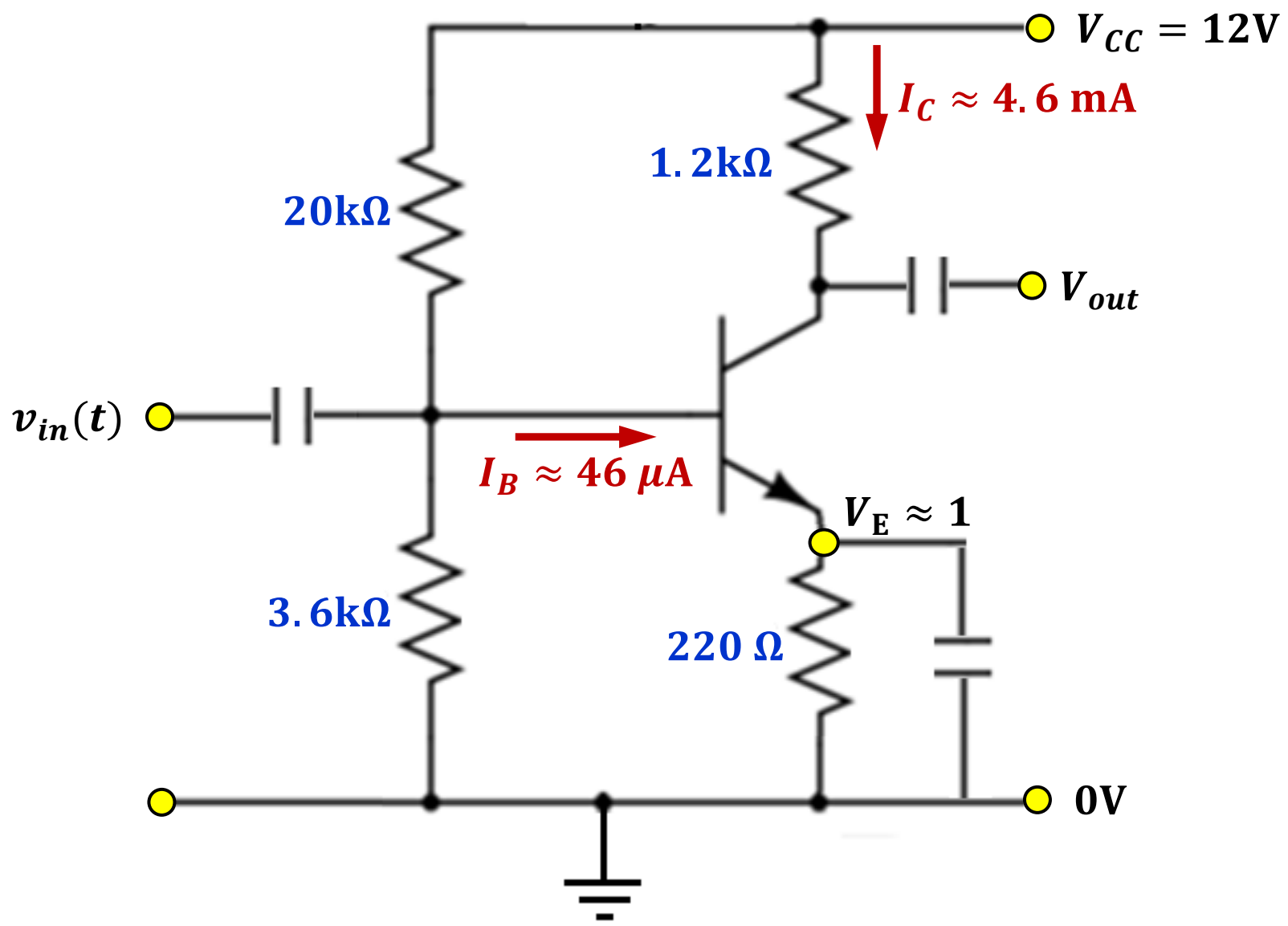
- How does a common emitter amplifier work?

# PRACTICAL DESIGN – Single battery bias

Emitter resistor added to improve stabilization if a decrease of supply voltage occurs

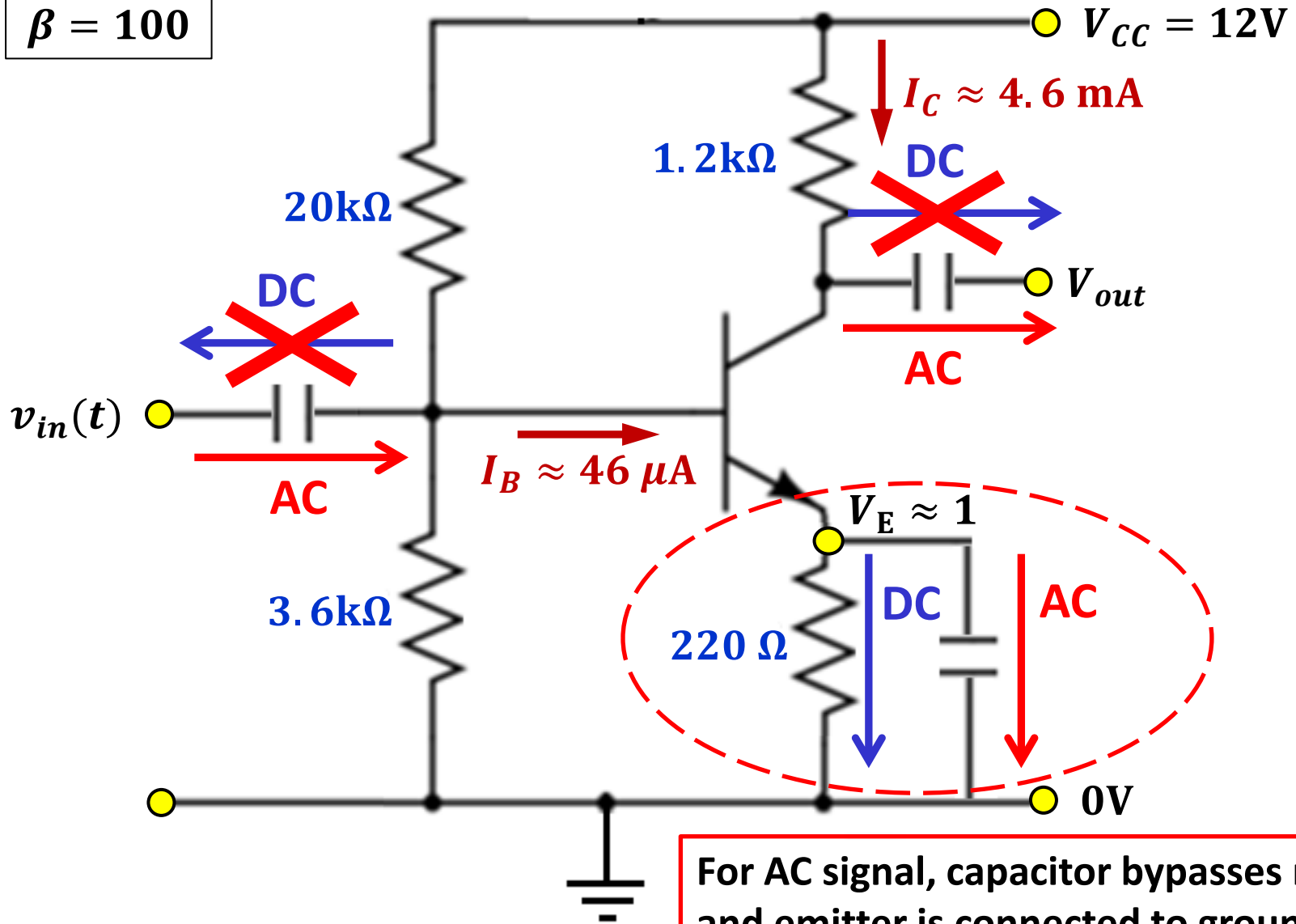


# PRACTICAL DESIGN – Coupling capacitors for A.C. signal



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$$\beta = 100$$



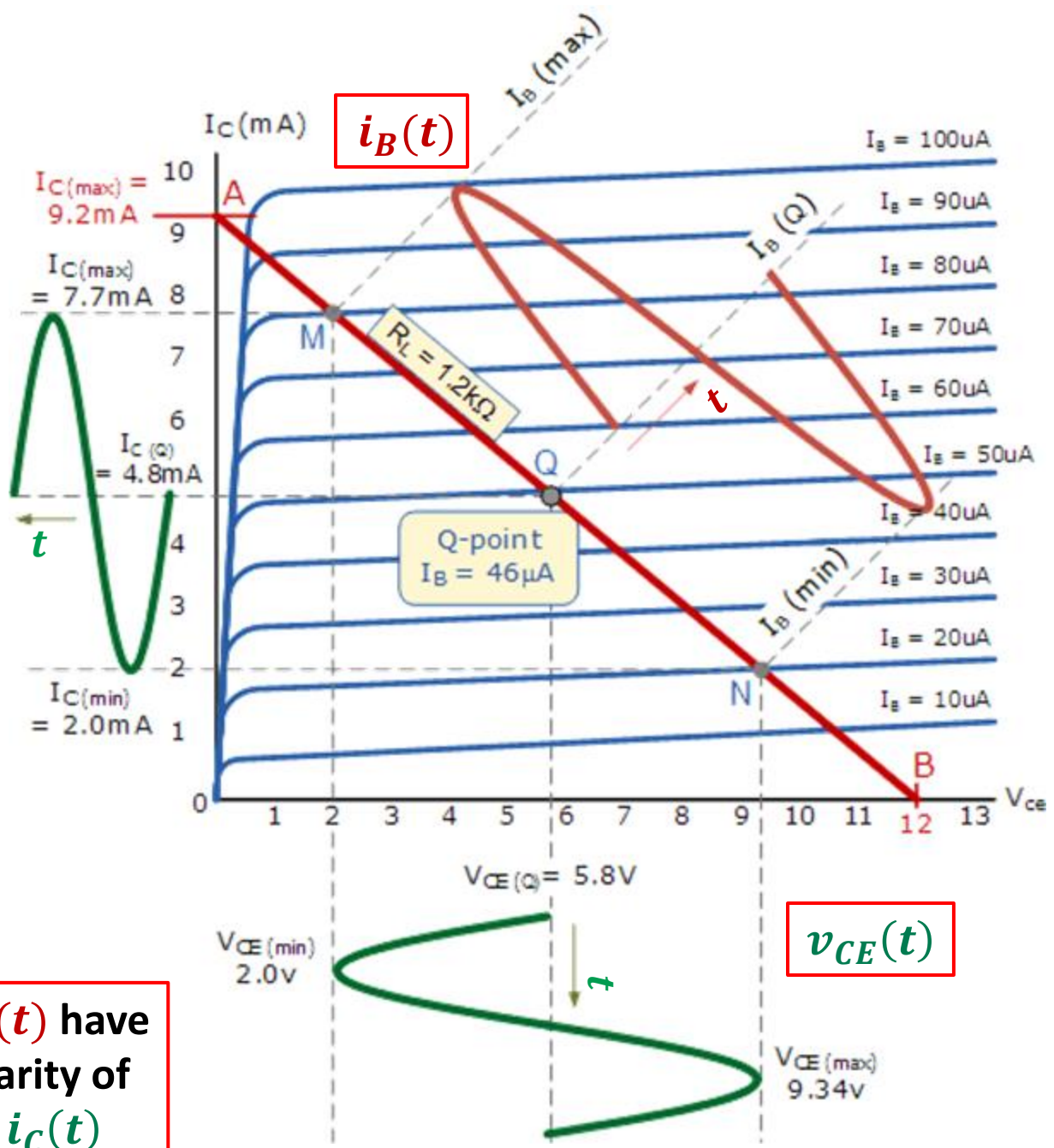
For AC signal, capacitor bypasses resistor and emitter is connected to ground

$i_C(t)$

$i_B(t)$

$v_{CE}(t)$

$v_{in}(t)$  and  $i_B(t)$  have opposite polarity of  $v_{CE}(t)$  and  $i_C(t)$



# Transistor stages can be cascaded to obtain more amplification

